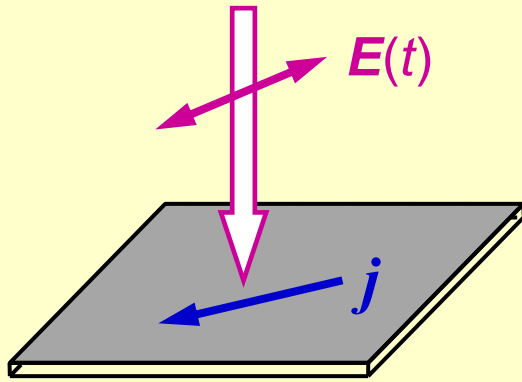

ФОТОГАЛЬВАНИЧЕСКИЕ ЭФФЕКТЫ В НИЗКОРАЗМЕРНЫХ СИСТЕМАХ - 1



С.А. Тарасенко

ФТИ им. А.Ф. Иоффе, Санкт-Петербург

ОТКЛИК НА ВЫСОКОЧАСТОТНОЕ ЭЛЕКТРИЧЕСКОЕ ПОЛЕ



E поле электромагнитной волны

$$E(\mathbf{r}, t) = E \exp(i\mathbf{q} \cdot \mathbf{r} - i\omega t) + E^* \exp(-i\mathbf{q} \cdot \mathbf{r} + i\omega t)$$

E – комплексная амплитуда

\mathbf{q} – волновой вектор

ω – частота

Электрический ток

линейный отклик

эффекты второго порядка

$$j_\alpha = \sum_{\beta} \sigma_{\alpha\beta} E_\beta + \sum_{\beta\gamma} P_{\alpha\beta\gamma} E_\beta E_\gamma^* + \sum_{\beta\gamma} D_{\alpha\beta\gamma} E_\beta E_\gamma + \dots$$

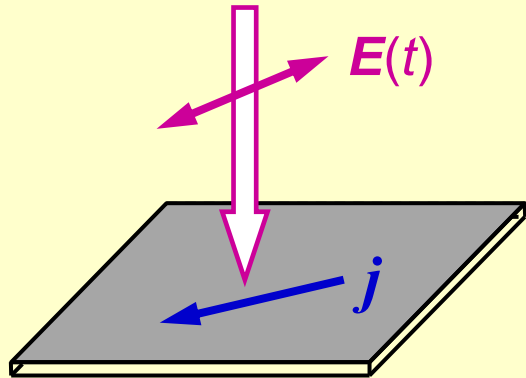
проводимость
поляризуемость

постоянный ток

ток на 2ω

ФОТОГАЛЬВАНИЧЕСКИЕ ЭФФЕКТЫ

Постоянный ток, квадратичный по амплитуде переменного поля



$$j_{\alpha} = \sum_{\beta\gamma} P_{\alpha\beta\gamma} E_{\beta} E_{\gamma}^{*}$$

Пространственная инверсия:

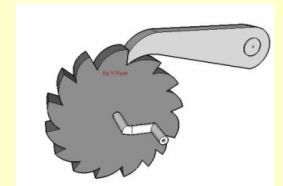
$$j \rightarrow -j, \quad E \rightarrow -E$$

ФГЭ в средах без центра инверсии

Нелинейный транспорт, эффект «храповика» (ratchet), nonlinear Hall effect

Ratchet is a device that allows continuous linear or rotary motion in only one direction while preventing motion in the opposite direction.

[http://en.wikipedia.org/wiki/Ratchet_\(device\)](http://en.wikipedia.org/wiki/Ratchet_(device))



Фотогальванические эффекты в оптике

B.I. Sturman and V.M. Fridkin, The photovoltaic and photorefractive effects in noncentrosymmetric materials (Gordon and Breach Science Publishers, 1992)

E.L. Ivchenko, Optical spectroscopy of semiconductor nanostructures (Springer, 2007)

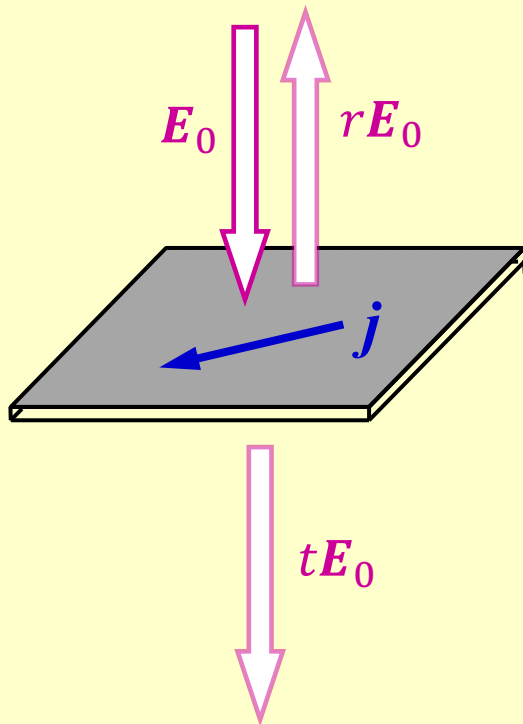
Основоположники теории:

В.И. Белиничер, Б.И. Стурман, М.В. Энтин, Л.И. Магарилл, Г.Е. Пикус, Е.Л. Ивченко

ПЛАН ЛЕКЦИИ

- **Линейный отклик на электромагнитное поле**
- Фотогальванические эффекты. Симметричный анализ
- Линейный и циркулярный ФГЭ в 2D структурах
 - микроскопическая модель, эксперимент
 - магнитоиндуцированные эффекты
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LINEAR RESPONSE OF 2D SYSTEM



Incident field

$$E_0(\mathbf{r}, t) = E_0 \exp(i\mathbf{q} \cdot \mathbf{r} - i\omega t) + \text{c. c.}$$

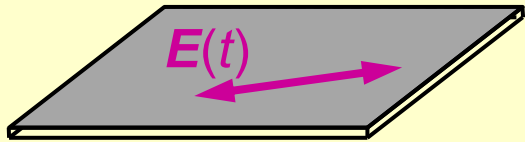
Linear response

$$\mathbf{j} = \sigma(\omega)\mathbf{E}$$

Amplitude reflection and transmission coefficient

$$r = -\frac{2\pi\sigma(\omega)/c}{1 + 2\pi\sigma(\omega)/c} \quad t = \frac{1}{1 + 2\pi\sigma(\omega)/c}$$

2D ELECTRON GAS. DRUDE CONDUCTIVITY



In-plane electric field

$$E_{\parallel}(t) = E_{\parallel} e^{-i\omega t} + \text{c.c.}$$

Newton equation for the drift velocity

$$\frac{d\mathbf{v}_d}{dt} = \frac{e}{m^*} \mathbf{E}_{\parallel}(t) - \frac{\mathbf{v}_d}{\tau} \quad \longrightarrow \quad \mathbf{v}_d = \frac{e\tau/m^*}{1 - i\omega\tau} \mathbf{E}_{\parallel} e^{-i\omega t} + \text{c.c.}$$

↙ momentum relaxation time

Momentum relaxation time

$$1/\tau = \frac{2\pi}{\hbar} \sum_{k'} \langle |V_{k'k}|^2 \rangle (1 - \cos \theta_{k'k}) \delta(\varepsilon_k - \varepsilon_{k'})$$

matrix elements of scattering

Drude conductivity

$$\sigma(\omega) = \frac{n_e e^2 \tau / m^*}{1 - i\omega\tau}$$

DRUDE MODEL. APPLICABILITY

Good conductivity

$$k_F l \gg 1 \quad (E_F \tau / \hbar \gg 1)$$

$$\sigma_0 = \frac{n_e e^2 \tau}{m^*} = \frac{\nu m^* E_F e^2 \tau}{2\pi \hbar^2 m^*} = \frac{\nu e^2 E_F \tau}{2\pi \hbar} \gg \frac{e^2}{h}$$

$$\frac{h}{e^2} \approx 25 \text{ k}\Omega$$

ν spin/valley degeneracy

von Klitzing constant

Classical range of frequencies

$$\hbar \omega \ll E_F$$

Otherwise, quantum description, e.g., Kubo formula

- Indirect optical transitions (scattering assisted)
- Direct optical transitions

ПЛАН ЛЕКЦИИ

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SYMMETRY CONSIDERATION

Photogalvanic effects (PGEs)

$$j_{\alpha} = \sum_{\beta\gamma} P_{\alpha\beta\gamma} E_{\beta} E_{\gamma}^*$$

Further analysis

$$j_{\alpha} = \sum_{\beta\gamma} L_{\alpha\beta\gamma} \frac{E_{\beta} E_{\gamma}^* + E_{\gamma} E_{\beta}^*}{2} + \sum_{\beta} C_{\alpha\beta} \underbrace{i[\mathbf{E} \times \mathbf{E}^*]}_{\text{axial vector}} \Big|_{\beta} \propto P_{\text{circ}}$$

linear ratchet or linear PGE
(piezoelectric systems)

LiNbO₃:Fe A.M. Glass et al. (1974)
Theory V.I. Belinicher et al. (1976)
E.M. Baskin et al. (1977)



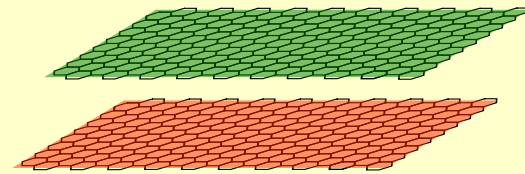
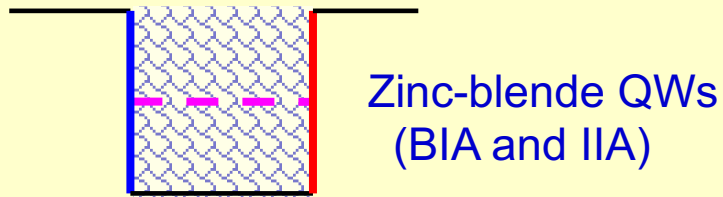
circular ratchet or circular PGE
(gyrotropic systems)

Pred. E.L. Ivchenko, G.E. Pikus (1978)
V.I. Belinicher (1978)
Exper in bulk Te V.M. Asnin et al (1978)



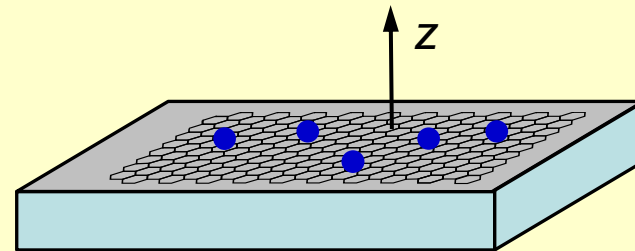
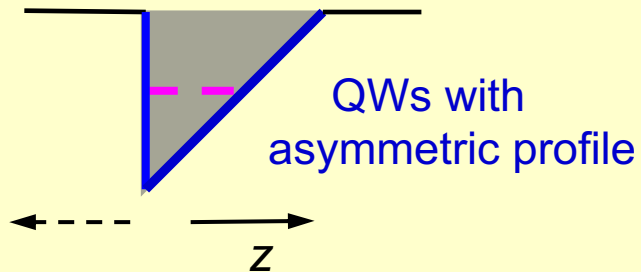
SPACE INVERSION ASYMMETRY IN 2D SYSTEMS

Bulk (or 2D “bulk”) inversion asymmetry (BIA)



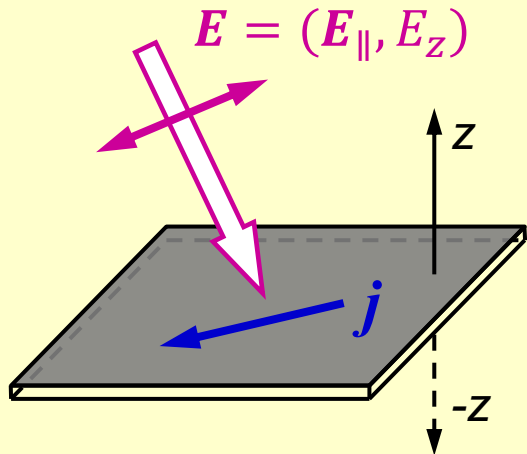
TMDC monolayers (D_{3h} group)
 MoS_2 , MoSe_2 , WSe_2 , ...

Structure inversion asymmetry (SIA)



2D crystal on substrate, special stacks

RATCHET TRANSPORT DUE TO STRUCTURE INVERSION ASYMMETRY



E_z is invariant

j and E_{\parallel} transform in a similar way

Density of dc electric current

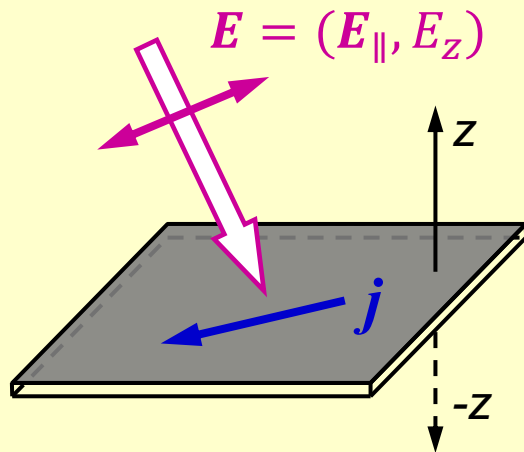
$$\mathbf{j} = L(\mathbf{E}_{\parallel} E_z^* + E_z^* \mathbf{E}_{\parallel}) + C i(\mathbf{E}_{\parallel} E_z^* - E_z^* \mathbf{E}_{\parallel})$$

linear ratchet

circular ratchet

oblique incidence of radiation is required

(I) AC CURRENT BY IN-PLANE COMPONENT E_{\parallel}



In-plane E -field component

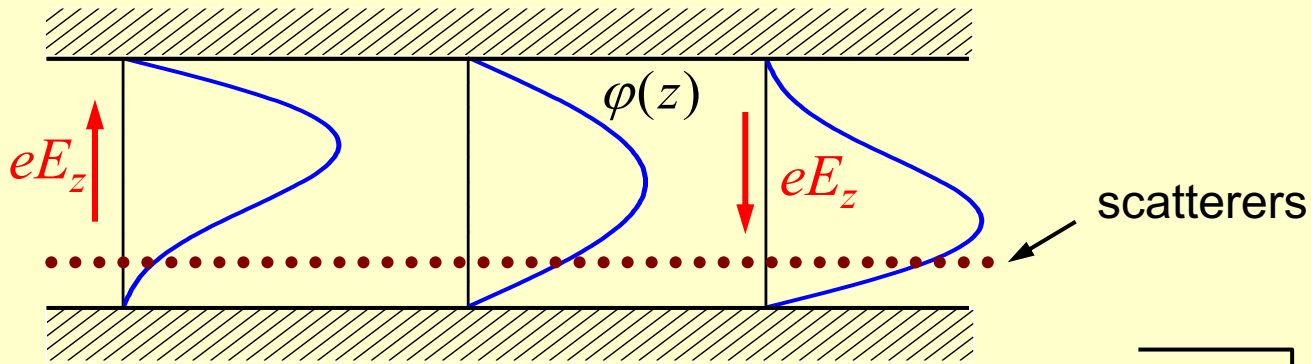
$$E_{\parallel}(t) = E_{\parallel} e^{-i\omega t} + \text{c.c.}$$

Equation for the drift velocity of electrons

$$\frac{d\mathbf{v}_d}{dt} = \frac{e}{m^*} \mathbf{E}_{\parallel}(t) - \frac{\mathbf{v}_d}{\tau} \quad \longrightarrow \quad \mathbf{v}_d = \frac{e\tau/m^*}{1 - i\omega\tau} \mathbf{E}_{\parallel} e^{-i\omega t} + \text{c.c.}$$

momentum relaxation time

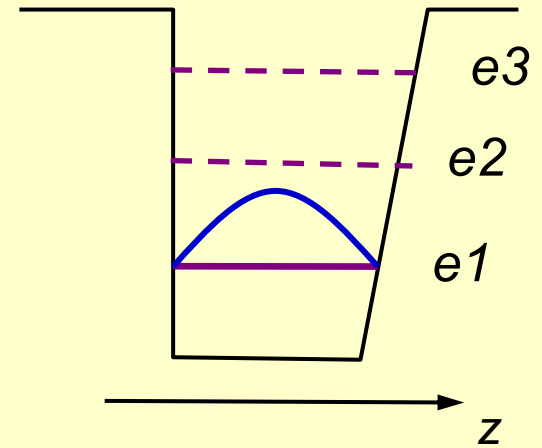
(II) OSCILLATIONS OF ELECTRON MOBILITY BY E_z



Admixture of excited subbands

Function of size quantization

$$\varphi(z) = \varphi_1(z) + eE_z(t) \sum_{n \neq 1} \frac{z_{n1}}{\varepsilon_{n1}} \varphi_n(z)$$

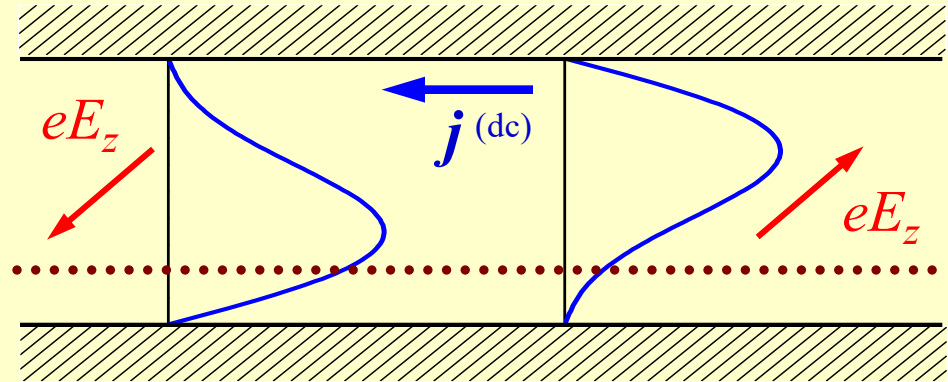
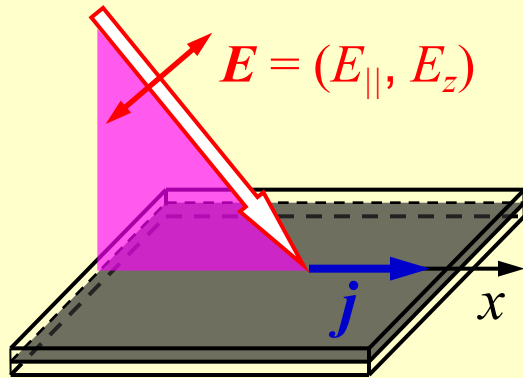


Momentum relaxation time

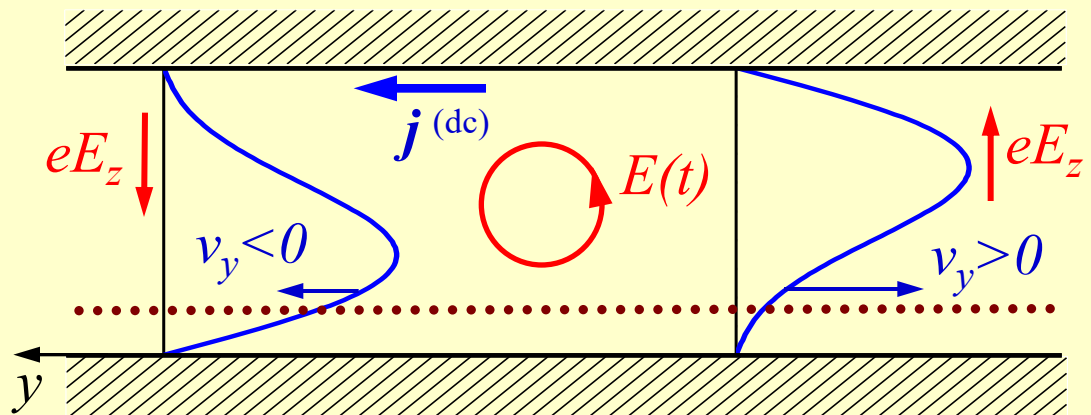
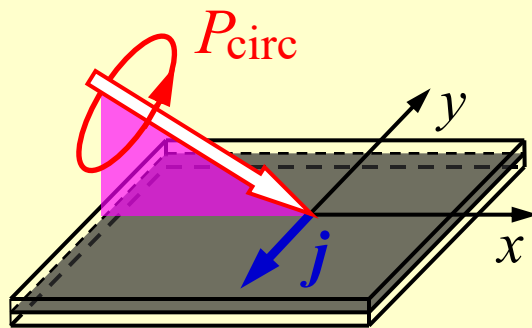
$$\frac{1}{\tau(t)} = \frac{1}{\tau_0} \left(1 + 4eE_z(t) \sum_{n \neq 1} \frac{z_{n1} \xi_n}{\varepsilon_{n1}} \right), \quad \xi_n = \langle V_{11} V_{1n} \rangle / \langle V_{11}^2 \rangle$$

MECHANISMS OF LINEAR AND CIRCULAR RATCHET

(a) Linearly polarized field



(b) Circularly polarized field



MICROSCOPIC THEORY. QUASI-CLASSICAL APPROACH

Newton equation for the drift velocity

$$\frac{d\mathbf{v}_d(t)}{dt} = \frac{e\mathbf{E}_{\parallel}(t)}{m^*} - \frac{\mathbf{v}_d(t)}{\tau(t)}$$

Momentum relaxation time

$$\frac{1}{\tau(t)} = \frac{1}{\tau_0} + \zeta eE_z(t)$$

Electric current

$$\mathbf{j}(t) = e\mathbf{v}_d(t)N_e$$

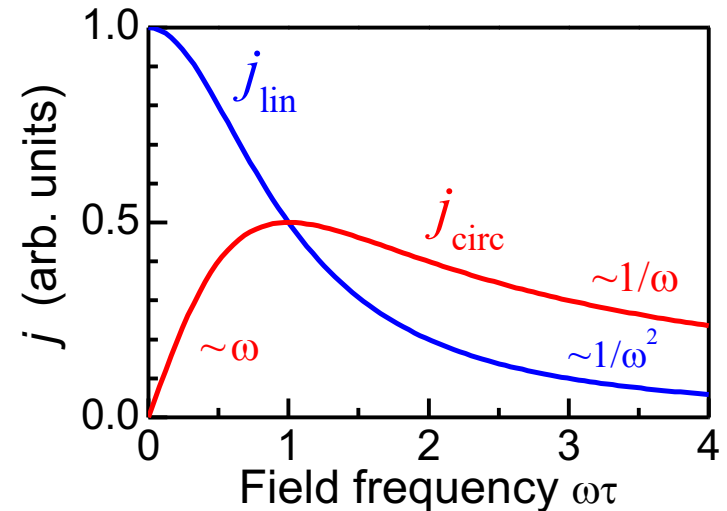
DC current

$$\mathbf{j} = -N_e \frac{\zeta e^3 \tau_0^2}{m^*} \left[\frac{\mathbf{E}_{\parallel} E_z^* + \mathbf{E}_z E_{\parallel}^*}{1 + (\omega\tau_0)^2} + i\omega\tau_0 \frac{\mathbf{E}_{\parallel} E_z^* - \mathbf{E}_z E_{\parallel}^*}{1 + (\omega\tau_0)^2} \right]$$

Linear ratchet

Circular ratchet

Frequency dependence of dc current



ЗАДАЧА

Генерация второй гармоники

Уравнение Ньютона для дрейфовой скорости

$$\frac{dv_d(t)}{dt} = \frac{eE_{\parallel}(t)}{m^*} - \frac{v_d(t)}{\tau(t)}$$

Электрическое поле

$$E(t) = E \exp(-i\omega t) + \text{c. c.}$$

Время релаксации по импульсу

$$\frac{1}{\tau(t)} = \frac{1}{\tau_0} + \zeta eE_z(t)$$

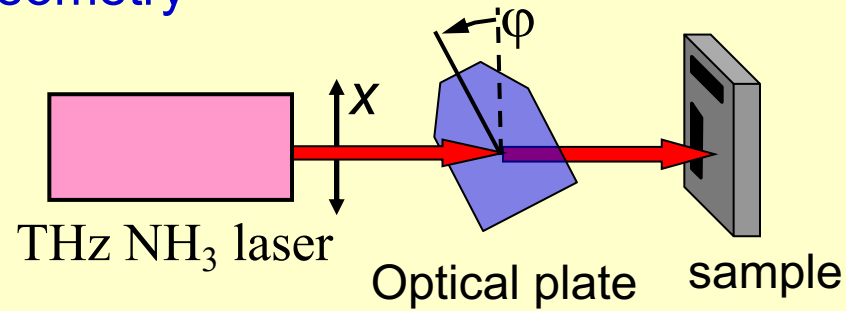
Плотность электрического тока

$$\mathbf{j}(t) = ev_d(t)N_e \quad \mathbf{j}(t) = (\mathbf{j}_1 e^{-i\omega t} + \text{c. c.}) + \mathbf{j}_{\text{dc}} + (\mathbf{j}_2 e^{-2i\omega t} + \text{c. c.})$$

Определить амплитуду тока на удвоенной частоте

EXPERIMENT

Experimental geometry



Electron channel on Si

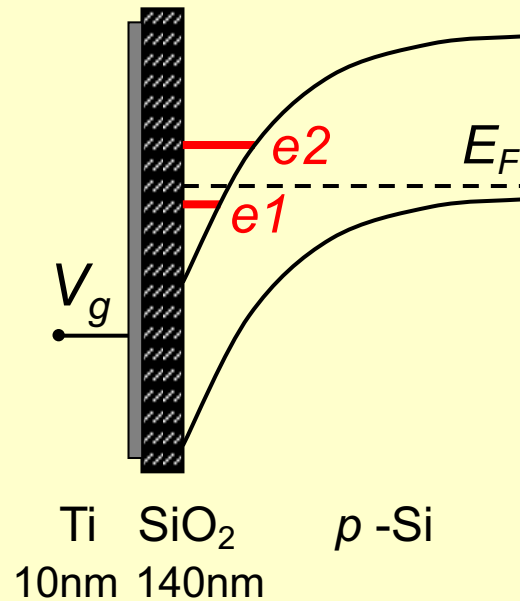
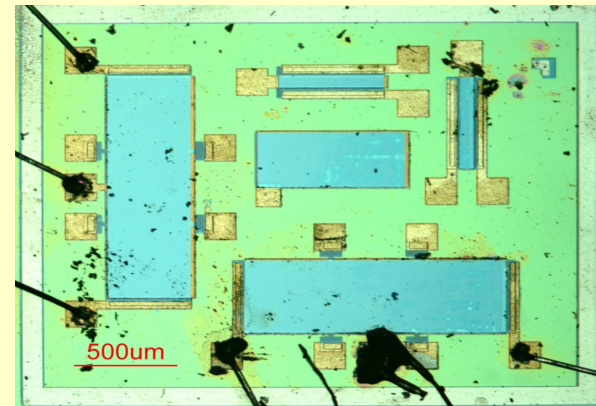
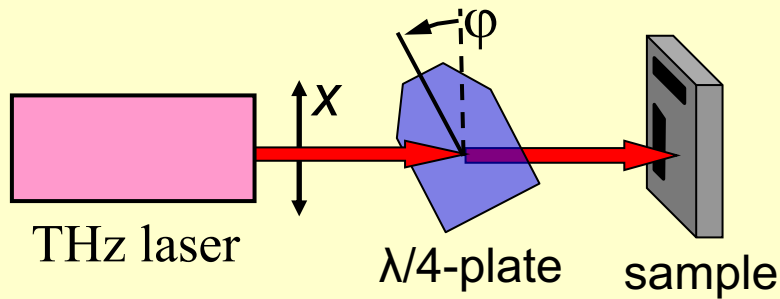


Photo of sample



Samples: Z.D. Kvon (Novosibirsk)
Experiment: S.D. Ganichev et al. (Regensburg)

EXPERIMENT: $\lambda/4$ OPTICAL PLATE



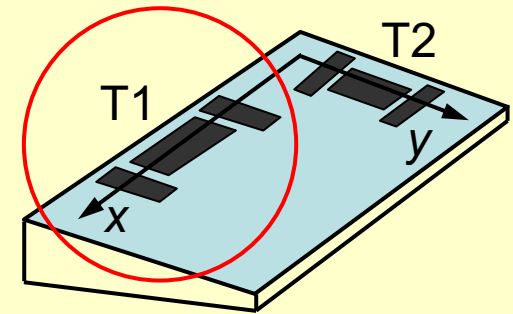
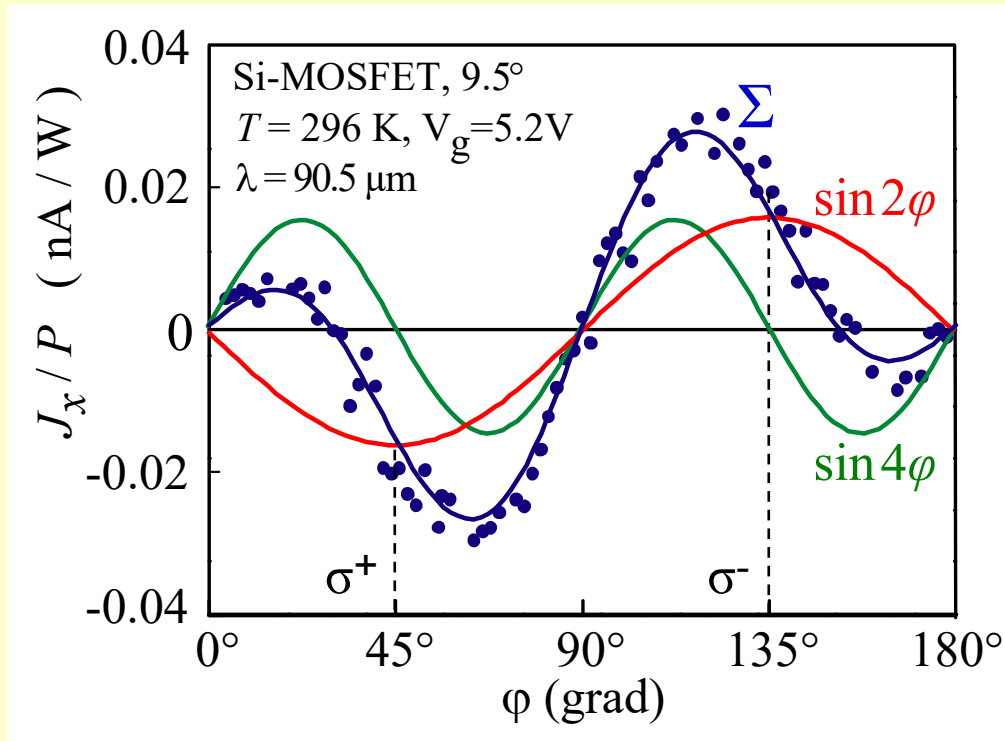
Polarization of THz radiation

$$P_{\text{circ}} = \sin 2\varphi$$

$$P_{\text{lin}} = \cos^2 2\varphi$$

$$P'_{\text{lin}} = (1/2) \sin 4\varphi$$

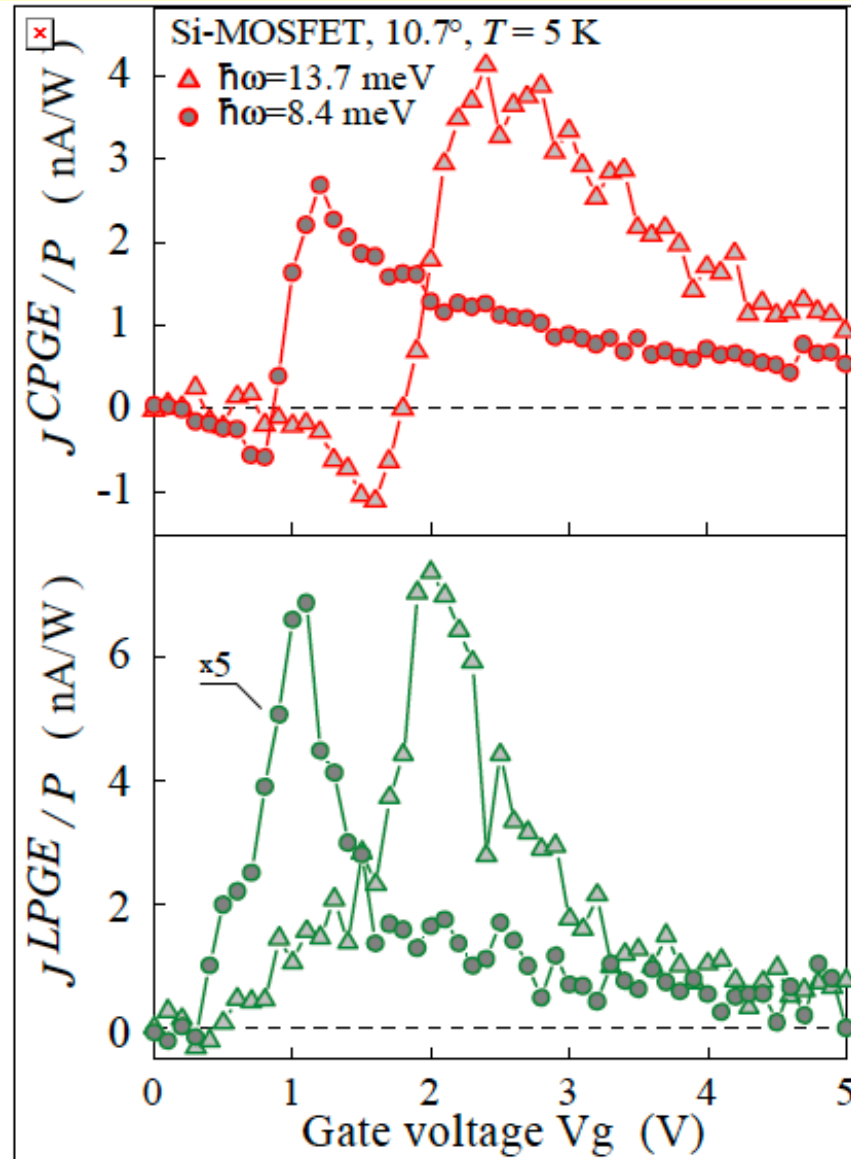
Polarization dependence of photocurrent



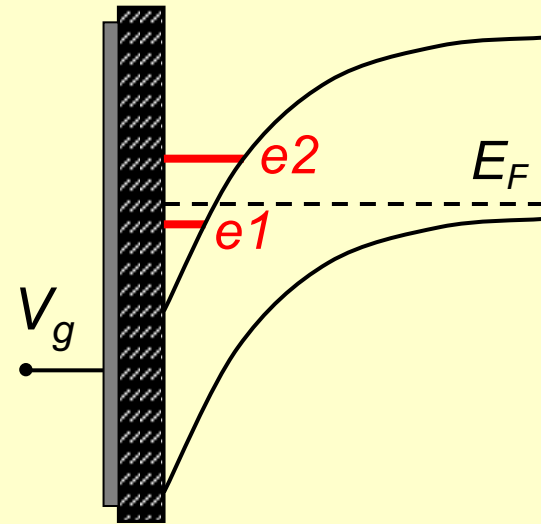
Electron channel
on Si surface (Si-MOSFET)

P. Olbrich et al.,
Phys. Rev. B (R) (2009)

EXPERIMENT: DEPENDENCE ON GATE VOLTAGE



2D electron gas on Si surface

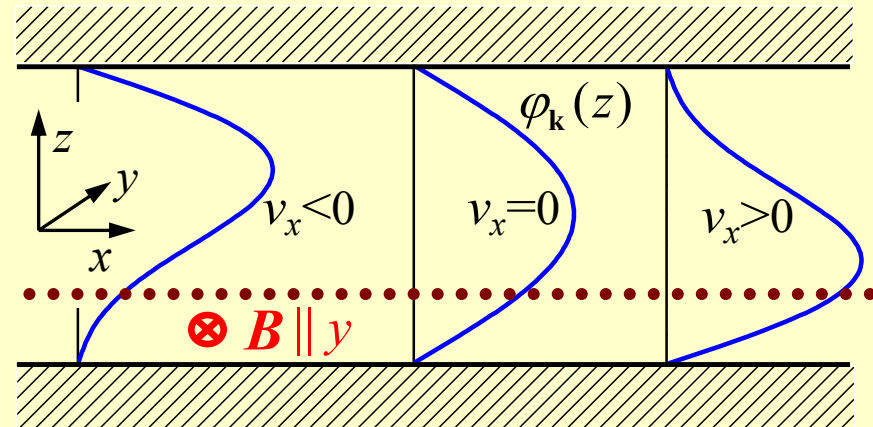
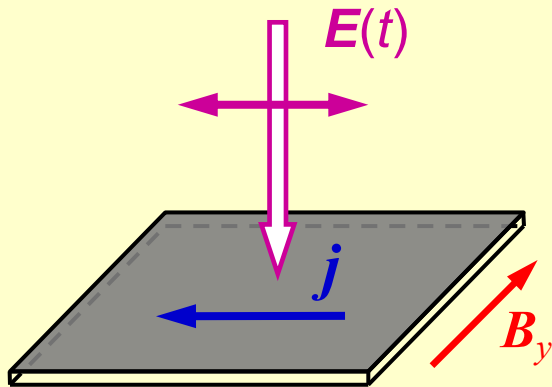


Intersubband resonance

$$\hbar\omega = \varepsilon_{21}$$

P. Olbrich et al.,
Phys. Rev. B (R) (2009)

MAGNETIC QUANTUM RATCHET EFFECT

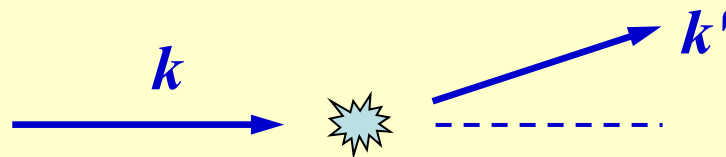


Up and down shift of electron density by Lorentz force

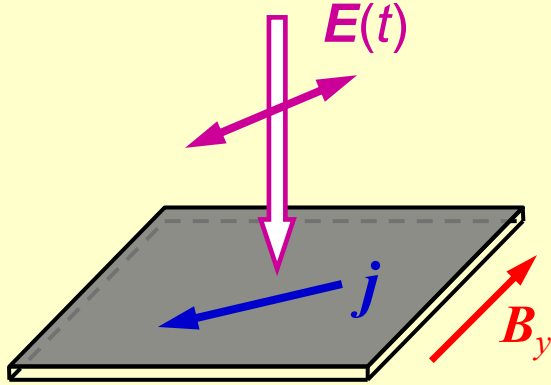
Probability of electron scattering $k \rightarrow k'$

$$W_{k'k} = W_0 + w_{\text{asym}} [B_x (k_y + k'_y) - B_y (k_x + k'_x)]$$

Asymmetry in scattering by static defects and phonons



MICROSCOPIC THEORY



Kinetic equation for distribution function $f(\mathbf{p}, t)$

$$\frac{\partial f}{\partial t} + e\mathbf{E}_{\parallel}(t) \cdot \frac{\partial f}{\partial \mathbf{p}} = I\{f\}$$

Collision integral

$$I\{f(\mathbf{p})\} = \sum_{\mathbf{p}'} [W_{\mathbf{p}\mathbf{p}'} f(\mathbf{p}') - W_{\mathbf{p}'\mathbf{p}} f(\mathbf{p})]$$

Expansion in the series of the electric field

$$f(\mathbf{p}, t) = f_0(\mathbf{p}) + \underbrace{[f_1(\mathbf{p})e^{-i\omega t} + \text{c. c.}]}_{\sim E} + \underbrace{f_2(\mathbf{p})}_{\sim EE^*}$$

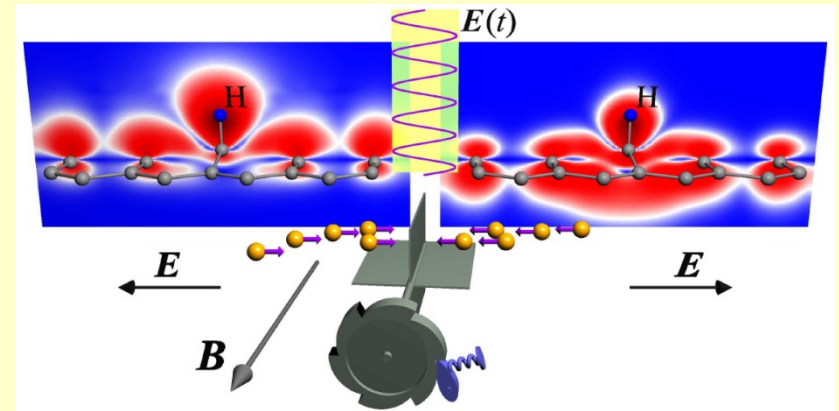
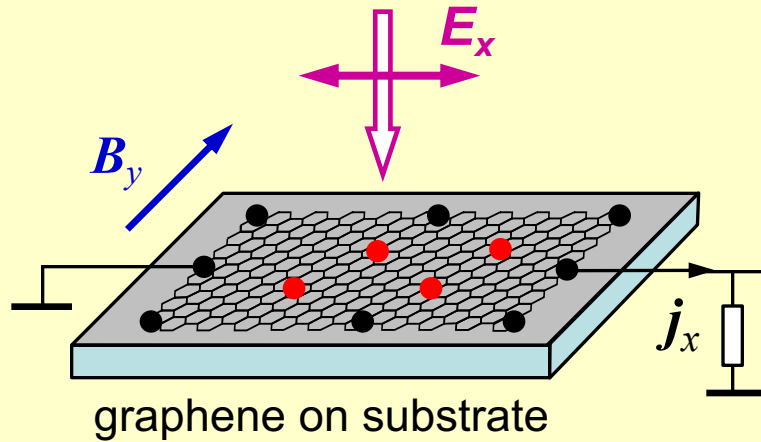
DC electric current

$$\mathbf{j} = ev \sum_{\mathbf{p}} \mathbf{v} f_2(\mathbf{p})$$

$$j_x = M_1(|E_x|^2 - |E_y|^2)B_y + M_2|\mathbf{E}|^2 B_y$$

$$j_y = M_1(E_x E_y^* + E_y E_x^*)B_y + M_3 i[\mathbf{E} \times \mathbf{E}^*]_z B_y$$

MAGNETIC QUANTUM RATCHET EFFECT IN GRAPHENE

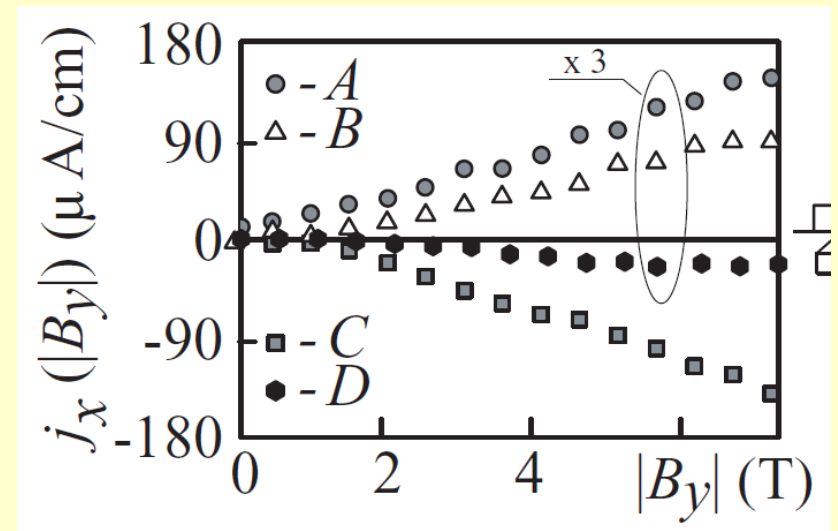


Samples

- (A,B,C) MBE-grown n-type monolayers on Si-terminated 4H-SiC(0001)
electron density $1.5 \div 7 \times 10^{12} \text{ cm}^{-2}$,
mobility $10^3 \text{ cm}^2/\text{Vs}$ at $T=300\text{K}$
- (D) CVD-grown monolayer

THz excitation

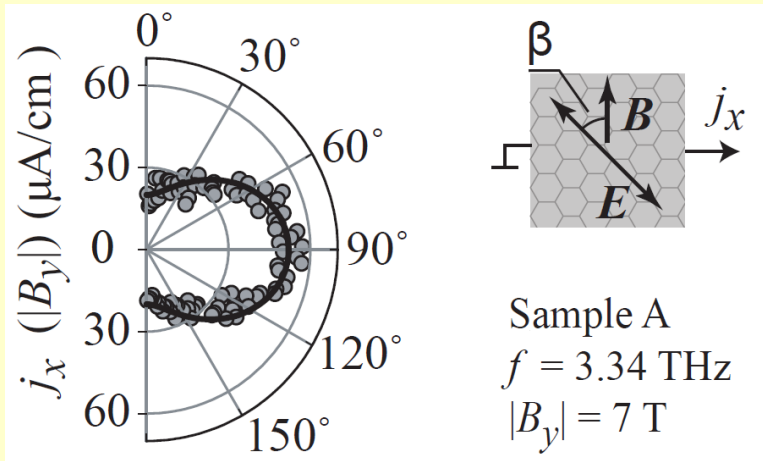
- cw laser CH_3OH ($\lambda = 118 \text{ }\mu\text{m}$, $P=0.5 \text{ mW}$)
- pulse laser NH_3 ($\lambda = 90.5, 148, 280 \text{ }\mu\text{m}$,
 $P=10 \text{ kW}$)



Magnetic field dependence

POLARIZATION DEPENDENCE

(i) Linear ratchet effect

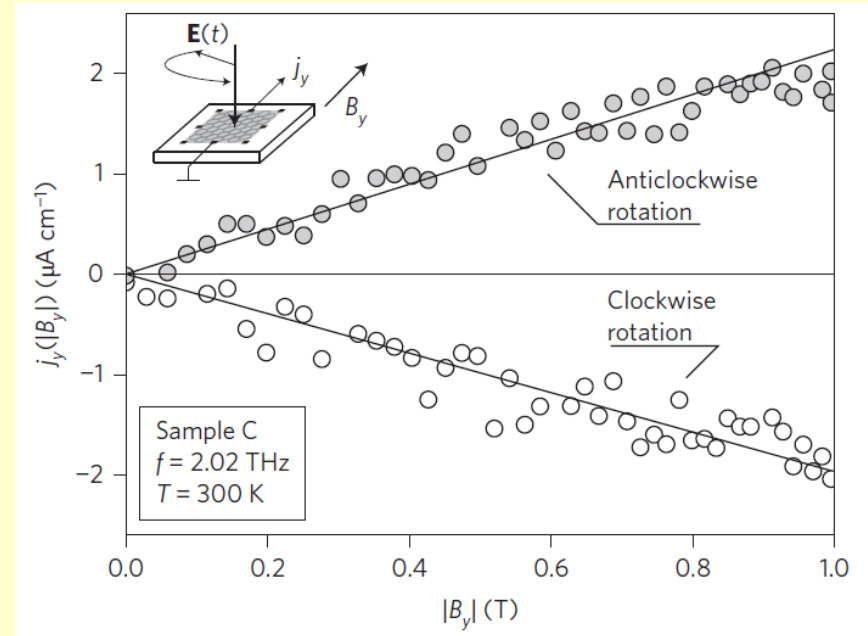


Polarization dependence

$$j_x = j_0 \cos 2\beta + j_1$$



(ii) Circular ratchet effect



Polarization dependence

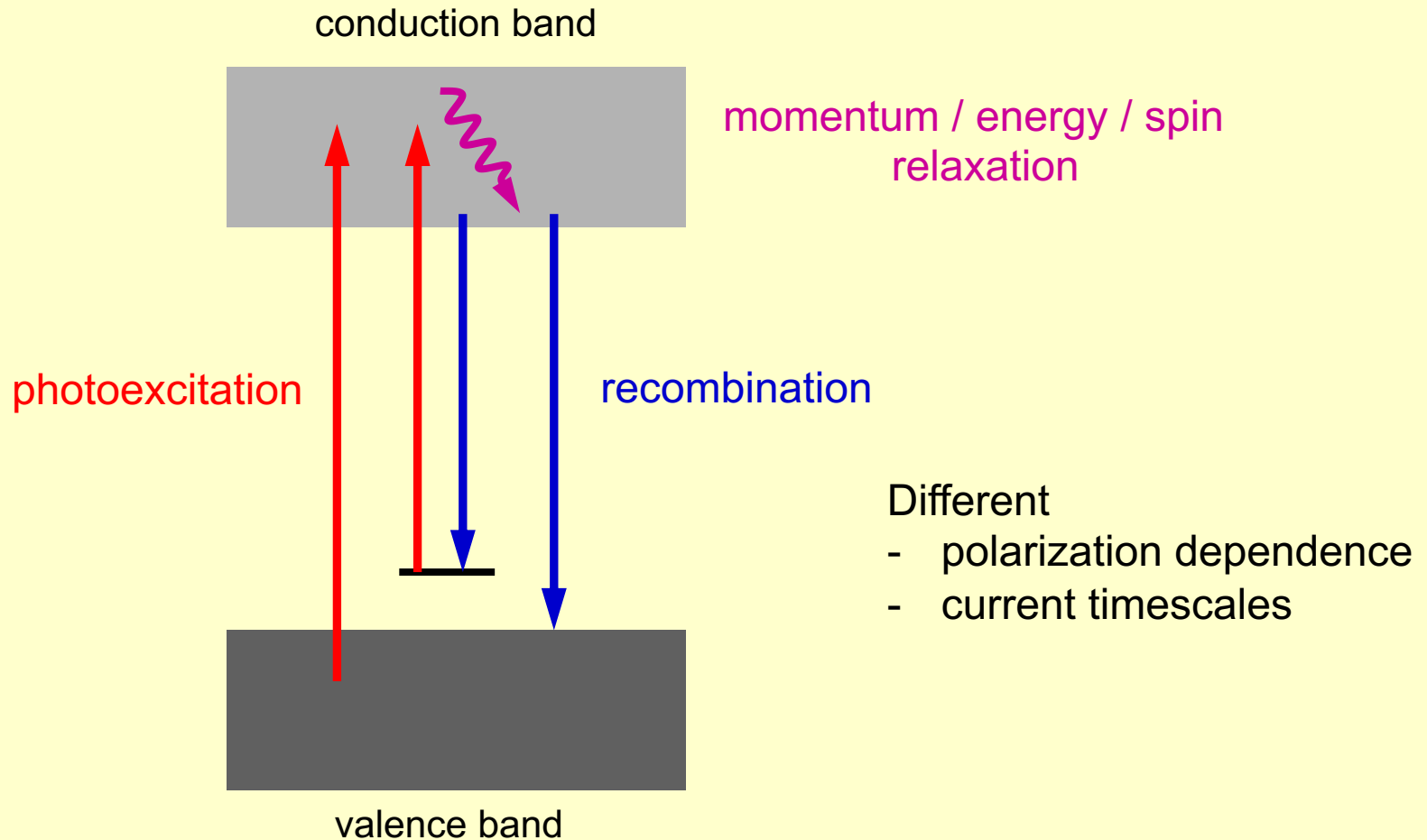
$$j_y \propto P_{circ}$$



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EXCITATION AND RELAXATION MECHANISMS



BALLISTIC AND SHIFT CONTRIBUTIONS

Most general description by density matrix

$$\rho_{nk, n'k'}$$

Bloch states

$$\psi_{nk} = \exp(i\mathbf{k} \cdot \mathbf{r}) u_{nk}(\mathbf{r})$$

Electric current $\mathbf{j} = e \text{Tr}(\mathbf{v}\rho) = e \text{Tr}\left(\frac{d\mathbf{r}}{dt}\rho\right)$

(i) Dominant contribution (typically)

$$\mathbf{j}_b = e \sum_{nk} v_{nk} f_{nk} \quad f_{nk} = \rho_{nk,nk} \text{ distribution function}$$

(ii) Shift (side-jump) contribution

$$\mathbf{j}_s = e \sum_{n \neq n', kk'} \mathbf{R}_{n'k',nk} W_{n'k',nk}$$

$$\mathbf{R}_{n'k',nk}$$

shift in real space

$$W_{n'k',nk}$$

transition probability

J.M. Luttinger, Phys. Rev. (1958)

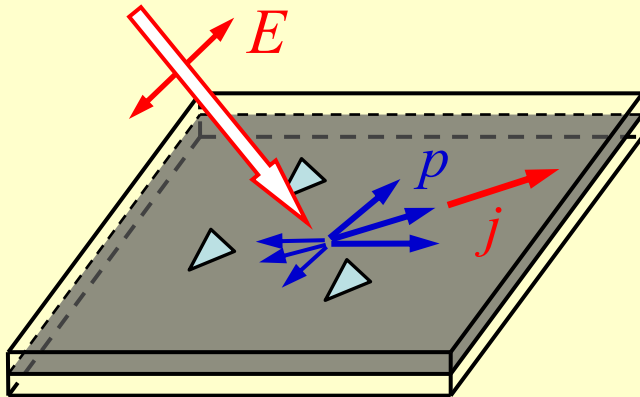
V.I. Belinicher, E.L. Ivchenko, B.I. Sturman, Sov. Phys. JETP (1982)

N.A. Sinitsyn, J. Phys.: Condens. Matter (2007)

L.E. Golub, E.L. Ivchenko, JETP (2011)

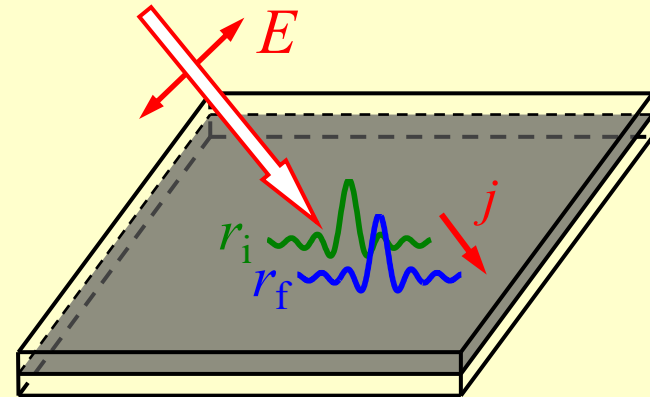
BALLISTIC AND SHIFT CONTRIBUTIONS

Ballistic current



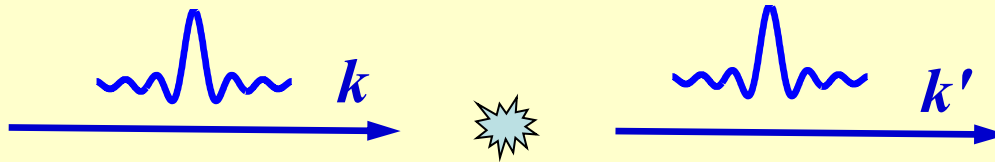
Asymmetry of distribution function in \mathbf{p} space

Shift current



Shift of electron wavepacket in \mathbf{r} space at quantum transition

SHIFT OF WAVEPACKET



$$\Psi_{k'} = e^{ik' \cdot r} \sum_k c_q e^{i\Phi(q)} e^{iq \cdot r}$$

The phase acquired at transition

$$\Phi(\mathbf{q}) \approx \Phi(0) + \nabla_{\mathbf{q}} \Phi \cdot \mathbf{q}$$

$$\Psi_{k'} = e^{ik' \cdot r} e^{+i\Phi(0)} \sum_k c_q e^{iq \cdot (r + \nabla_{\mathbf{q}} \Phi)}$$

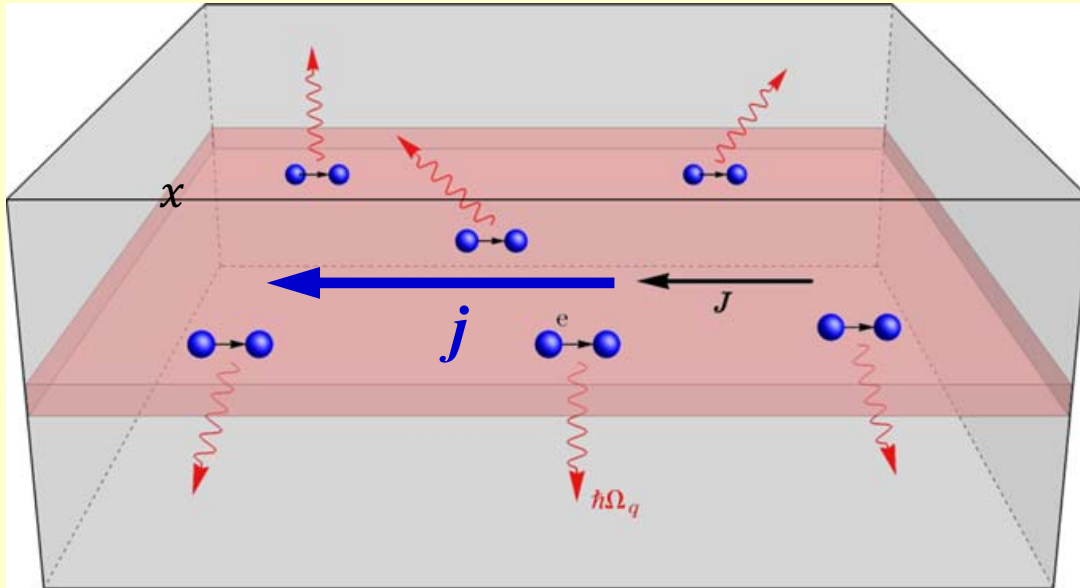
Shift of the Bloch electron

$$\mathbf{R}_{n'k', nk} = -(\nabla_{\mathbf{k}} + \nabla_{\mathbf{k}'}) \Phi_{n'k', nk} + \Omega_{n'k'} - \Omega_{nk}$$

Bloch states $\psi_{nk} = e^{ik \cdot r} u_{nk}(\mathbf{r})$ $\Omega_{sk} = i \langle u_{sk} | \nabla_{\mathbf{k}} | u_{sk} \rangle$

Berry connection

CURRENT BY ENERGY RELAXATION



(011)-grown zinc-blende-type quantum wells

Electric current

$$j_x \propto W$$

$$x \parallel [100]$$

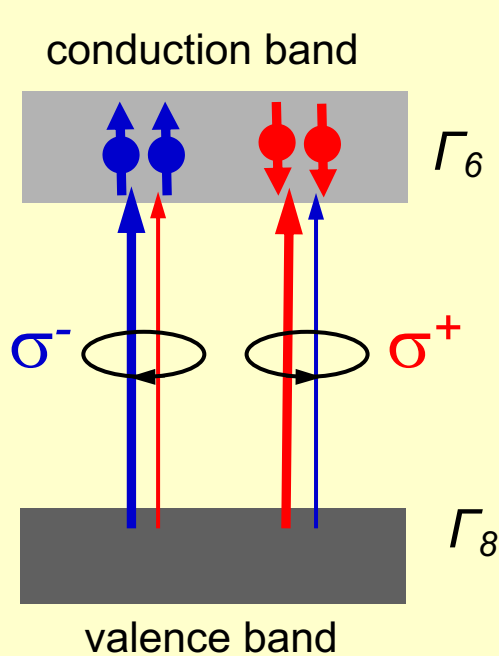
Estimations

$$j_x \sim 3\mu\text{A}/\text{cm}$$

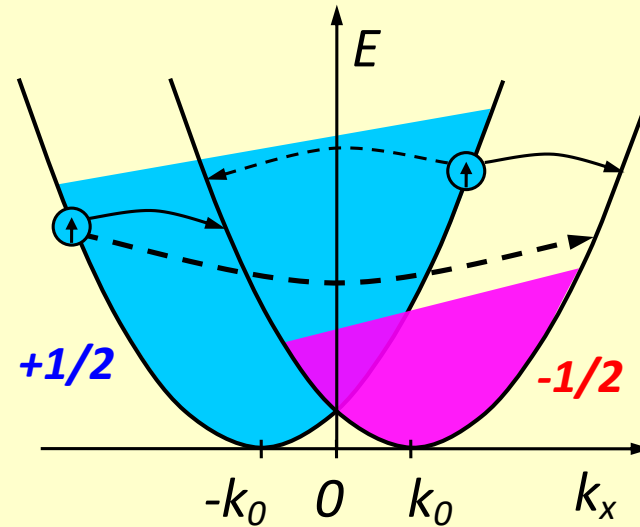
$$\text{@ } W = 1 \text{ W}/\text{cm}^2$$

HgTe-based QWs

OPTICAL ORIENTATION AND SPIN-GALVANIC EFFECT



Mechanisms based on k -linear terms



Current

$$j_{\alpha} \propto \left(\frac{dS_{\beta}}{dt} \right)_{\text{rel}}$$

Hamiltonian of k -linear spin-orbit splitting

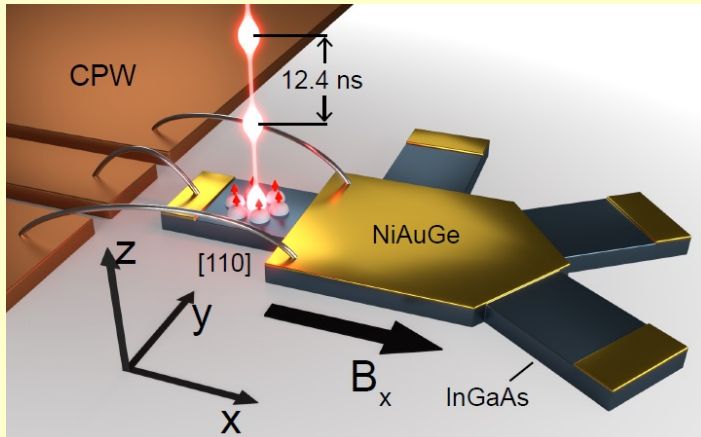
$$H_{SO} = \beta_{xy} \sigma_x k_y + \beta_{yx} \sigma_y k_x$$

(001) QWs, Rashba + Dresselhaus terms, $x \parallel [1\bar{1}0]$, $y \parallel [110]$

E.L. Ivchenko, Yu.B. Lyanda-Geller, G.E. Pikus, JETP (1990)
S.D. Ganichev, E.I. Ivchenko, V.V. Belkov, S.A.T. et al., Nature (2002)

CURRENT BY SPIN PRECESSION IN MAGNETIC FIELD

Experimental geometry



$\text{In}_{0.07}\text{Ga}_{0.93}\text{As}$ epilayers
thickness 500 nm, $n \sim 3 \times 10^{16} \text{ cm}^{-2}$

Experiment by

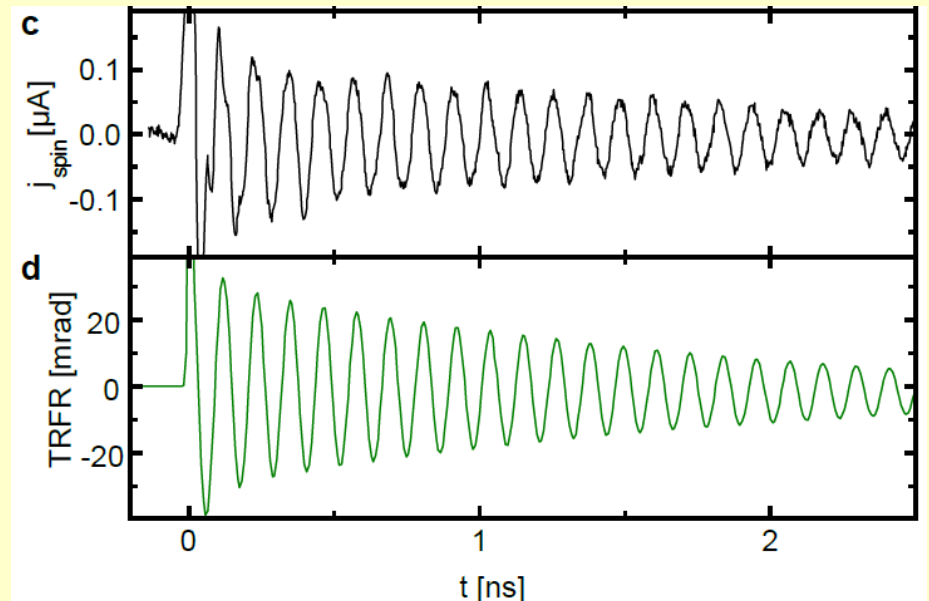
I. Stepanov, M. Ersfeld, B. Beschoten
RWTH Aachen University

M. Lepsa, *Forschungszentrum Jülich*

Time dependence of

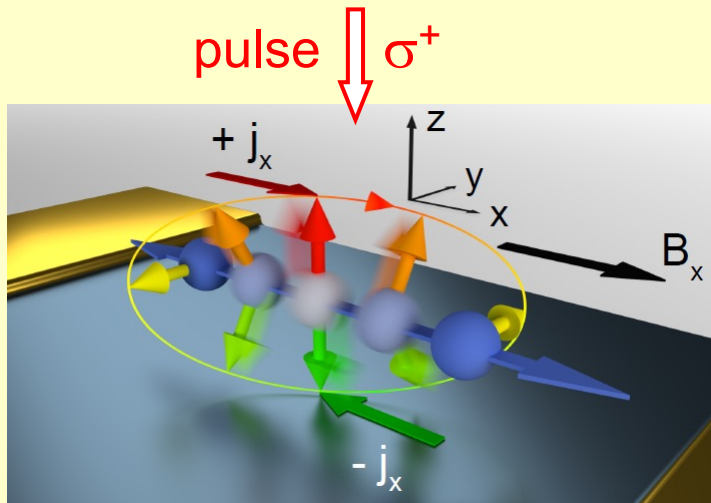
(c) electric signal

(d) spin Faraday rotation angle



optical excitation by Ti:sapphire laser, 3 ps pulse
temperature 50 K, magnetic field $B_x = 1 \text{ T}$

MICROSCOPIC CONSIDERATION



Hamiltonian

$$H = \frac{\hbar^2 k^2}{2m} + \beta_{yx} \sigma_y k_x + \frac{\hbar}{2} \Omega_L \sigma_x$$

k -linear SOI Zeeman

Velocity operator

$$\hat{v}_x = \frac{i}{\hbar} [H, x] = \frac{\hbar k_x}{m} + \frac{\beta_{yx}}{\hbar} \sigma_y$$

Упражнение

$$[H, \hat{v}_x] = \beta_{yx} \Omega_L \sigma_z$$

velocity is not conserved

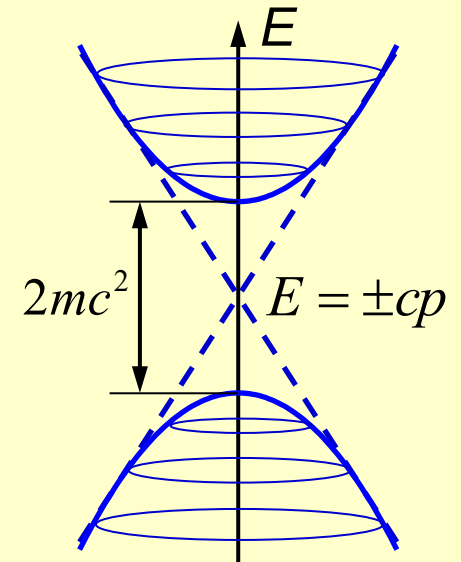
ZITTERBEWEGUNG OF DIRAC PARTICLES



P. Dirac

Relativistic wave equation
for spin-1/2 particle, 1928

$$i\hbar \frac{\partial \Psi}{\partial t} = H\Psi, \quad H = \begin{pmatrix} mc^2 & c\boldsymbol{\sigma} \cdot \mathbf{p} \\ c\boldsymbol{\sigma} \cdot \mathbf{p} & -mc^2 \end{pmatrix}$$



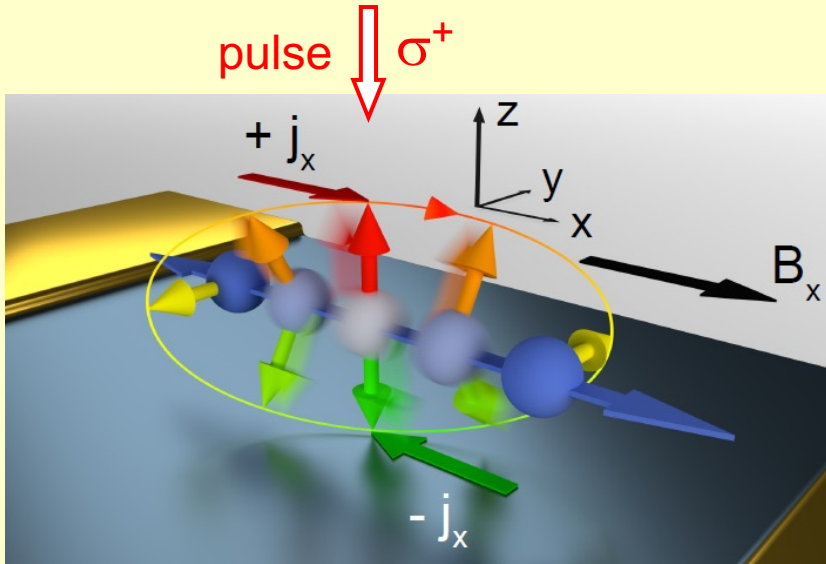
E. Schrödinger

Velocity operator

$$\mathbf{v} = \frac{d\mathbf{r}}{dt} = \frac{i}{\hbar} [H, \mathbf{r}] = c \begin{pmatrix} 0 & \boldsymbol{\sigma} \\ \boldsymbol{\sigma} & 0 \end{pmatrix}$$

$[H, \mathbf{v}] \neq 0$ **velocity is not conserved**

COHERENT ELECTRON ZITTERBEWEGUNG



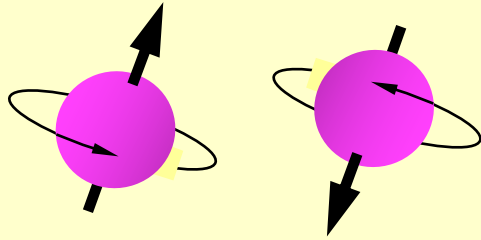
AC electric current as coherent Zitterbewegung

$$j_x(t) = 2n\tau_p \frac{\beta_{yx}}{\hbar} \frac{ds_y(t)}{dt}$$

ПЛАН ЛЕКЦИИ

- Линейный отклик на электромагнитное поле
- Фотогальванические эффекты. Симметричный анализ
- Линейный и циркулярный ФГЭ в 2D структурах
 - микроскопические механизмы, эксперимент
 - магнитоиндуцированные эффекты
 - токи, обусловленные энергетической и спиновой релаксацией
- Спиновые и долинные фототоки
- Основные результаты

SPIN AND VALLEY DEGREES OF FREEDOM



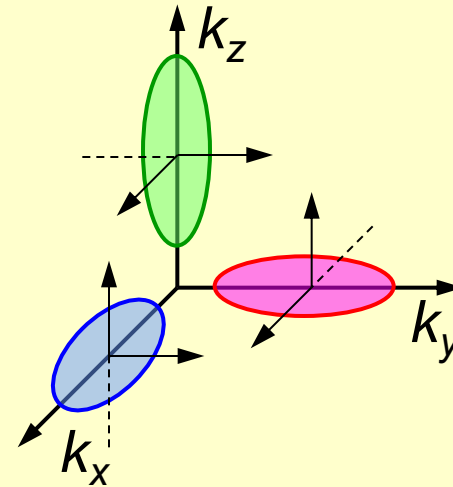
Selective population of spin subbands
by circularly polarized light
(optical orientation of electron spins)

G. Lampel, Phys. Rev. Lett. (1968)

Optical injection of spin currents

R.D.R. Bhat et al., Phys. Rev. Lett. (2005)
S.A.T. and E.L. Ivchenko, JETP Lett. (2005)

H. Zhao et al., Phys. Rev. B (2005)
S.D. Ganichev et al., Nature Phys. (2006)



Selective population of valleys
by linearly polarized light

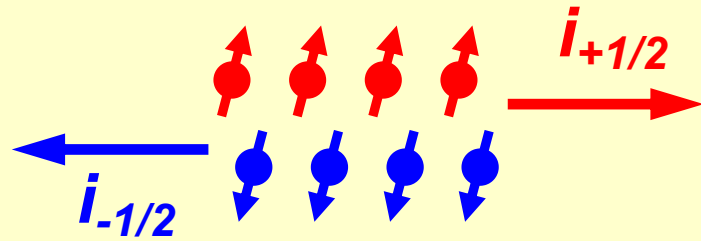
A.A. Kaplyanskii et al., Solid State Comm. (1976)

Optical injection of valley currents

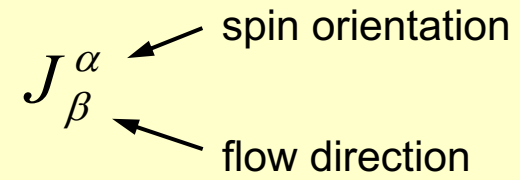
S.A.T. and E.L. Ivchenko, JETP Lett. (2005)
J. Karch et al., Phys. Rev. B (2011)

PURE SPIN CURRENTS

Pure spin current



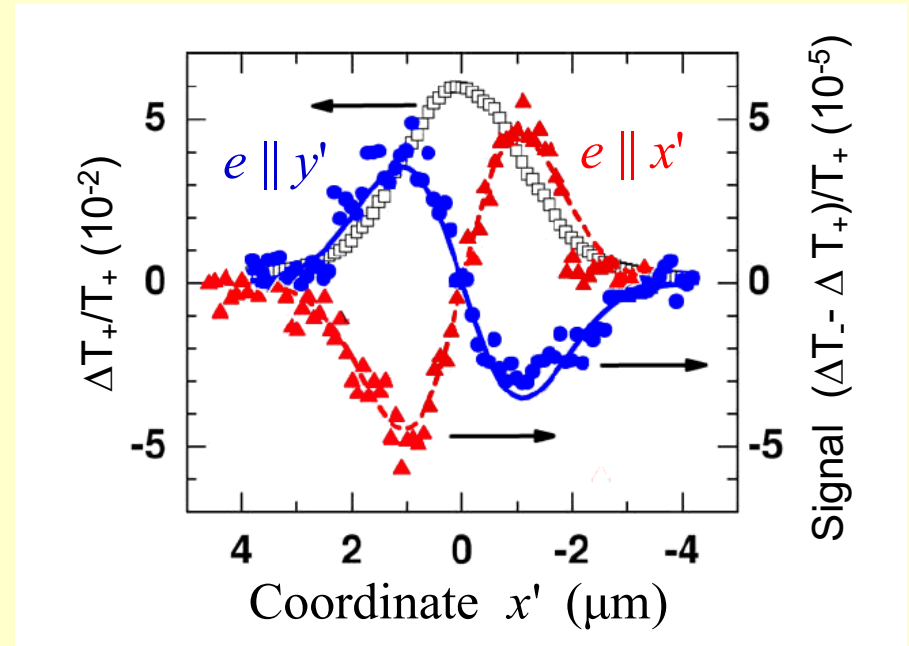
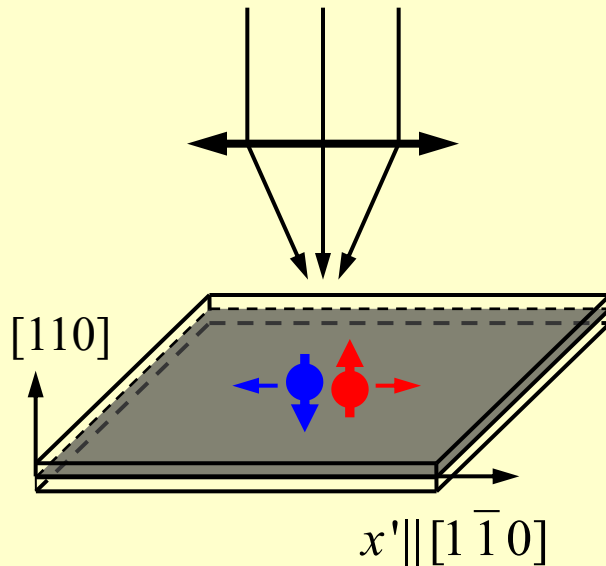
Second-rank tensor



SPIN CURRENT: INTERBAND EXCITATION

H. Zhao, X. Pan, A.L. Smirl et al., Phys. Rev. B 2005

Pump-probe technique with high spatial resolution



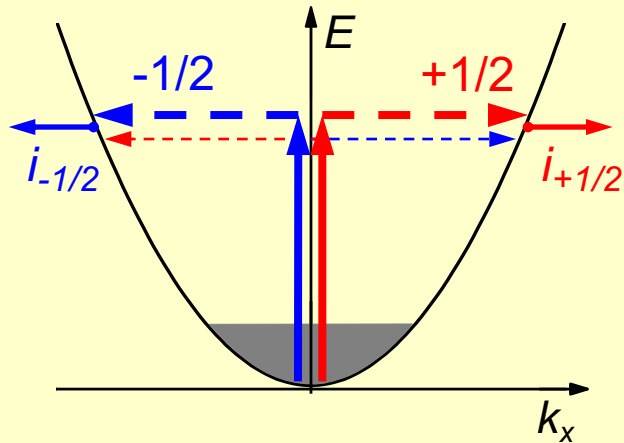
GaAs/AlGaAs (110)-grown quantum wells,
temperature $T=300\text{K}$

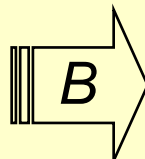
See also

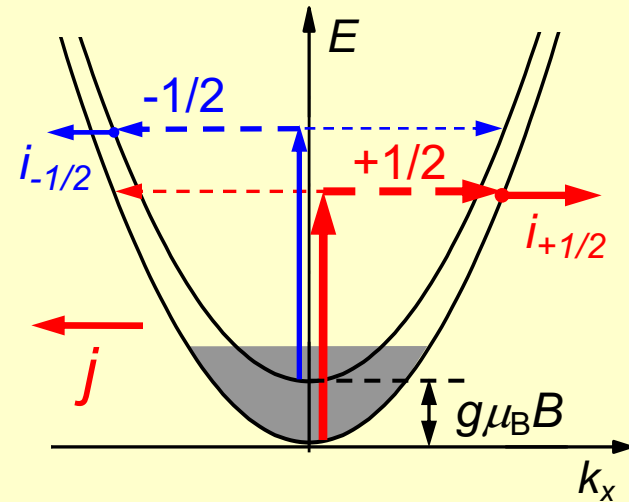
Y. Han, S. Xiao, H. Zhao et al., Appl. Phys. Lett. 2007 (detection by 2nd harmonic generation)

X.-D. Cui, Sh.-Q. Shen, J. Li et al., Appl. Phys. Lett. 2007 (electric measurements)

SPIN CURRENTS: FREE-CARRIER ABSORPTION




 magnetic field



Pure spin current J_β^α

$$\mathbf{j} = e(\mathbf{i}_{+1/2} + \mathbf{i}_{-1/2}) = 0$$

Electric current

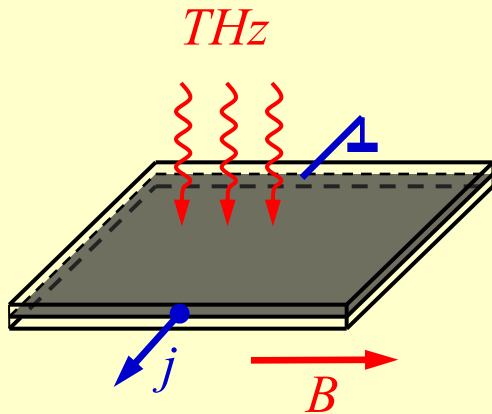
$$j_\beta = 4e \sum_\alpha J_\beta^\alpha s_\alpha$$

Spin-dependent electron scattering

$$V_{\mathbf{k}'\mathbf{k}} = V_0 + \sum_{\alpha\beta} V_{\alpha\beta} \hat{\sigma}_\alpha (k_\beta + k'_\beta)$$

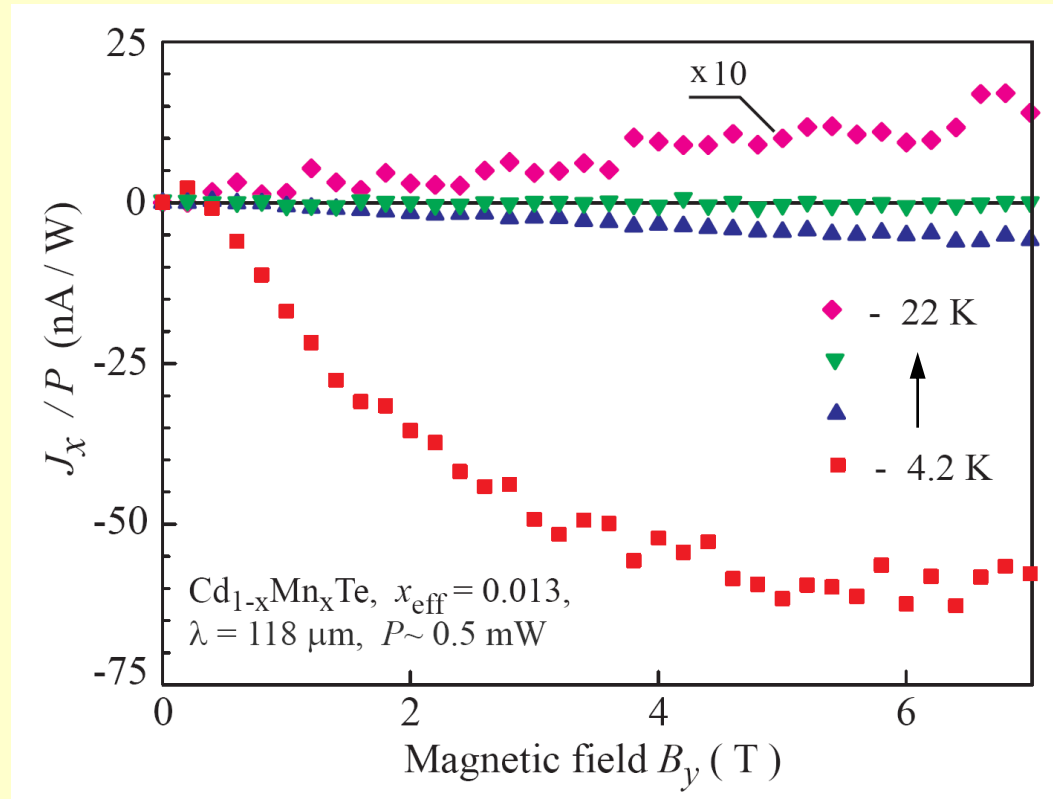
EXPERIMENT: MAGNETIC-FIELD-INDUCED CURRENT

Geometry of experiment



Electric current
at low temperatures

$$j \propto S^{\text{Mn}}$$



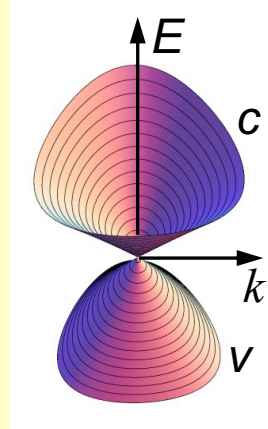
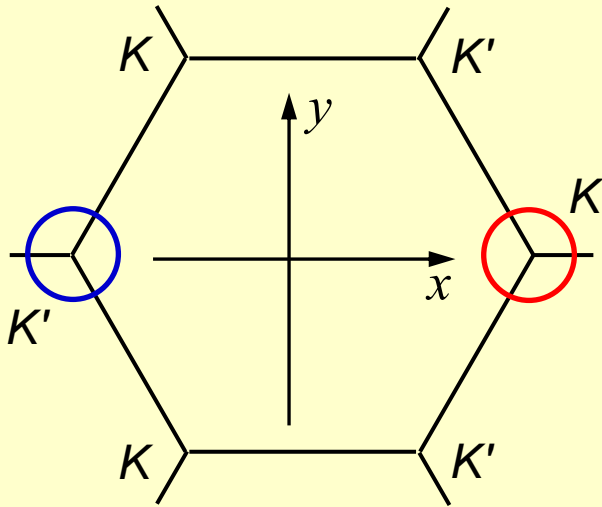
CdMnTe/CdMgTe (001) quantum wells

S.D. Ganichev, S.A.T., V.V. Bel'kov et al., PRL 102, 156602 (2009)

P. Olbrich, C. Zoth, P. Lutz et al., PRB 86, 085310 (2012)

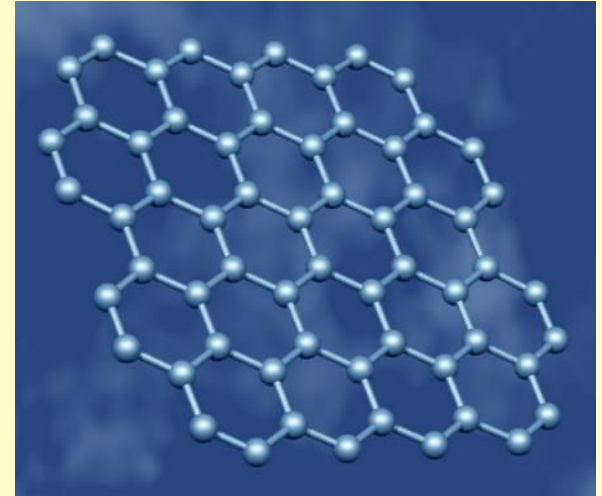
BAND STRUCTURE OF GRAPHENE

Brillouin zone of graphene



close to K -point
(D_{3h} group)

Crystal lattice of graphene



Point group D_{6h}

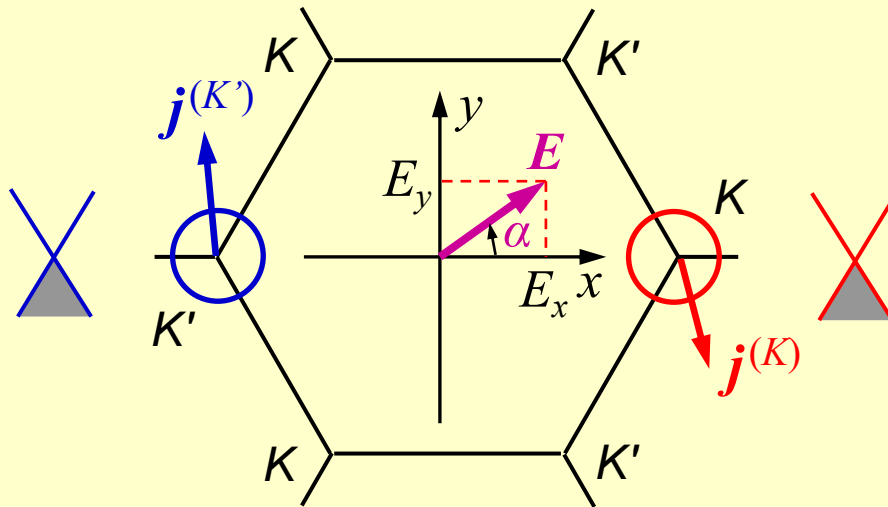
Effective Hamiltonian at the K point of the Brillouin zone

$$\hat{H} = \begin{pmatrix} 0 & \Omega_p \\ \Omega_p^* & 0 \end{pmatrix}, \quad \Omega_p = v_0(p_x - ip_y) - \mu(p_x + ip_y)^2$$

trigonal warping

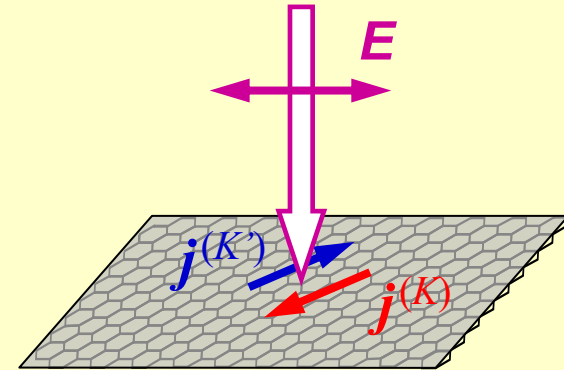
Review: A.H. Castro Neto, F. Guinea, N.M.R. Peres, K.S. Novoselov, and A.K. Geim, Rev. Mod. Phys. **81**, 109 (2009)

PURE VALLEY PHOTOCURRENTS



D_{3h} group
(no center of inversion)

Experimental geometry



D_{6h} point-group symmetry
(center of inversion)

Photocurrents in the K и K' valleys: $\mathbf{j}^{(K')} = -\mathbf{j}^{(K)}$

$$j_x^{(K)} = \chi (|E_x|^2 - |E_y|^2) \propto |E|^2 \cos 2\alpha$$

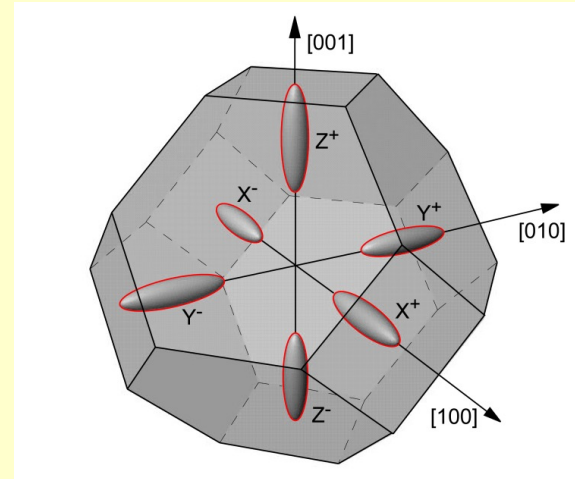
$$j_y^{(K)} = -\chi (E_x E_y^* + E_y E_x^*) \propto |E|^2 \sin 2\alpha$$

L.E. Golub, S.A.T., M.V. Entin, and L.I. Magarill, Phys. Rev. B (2011)

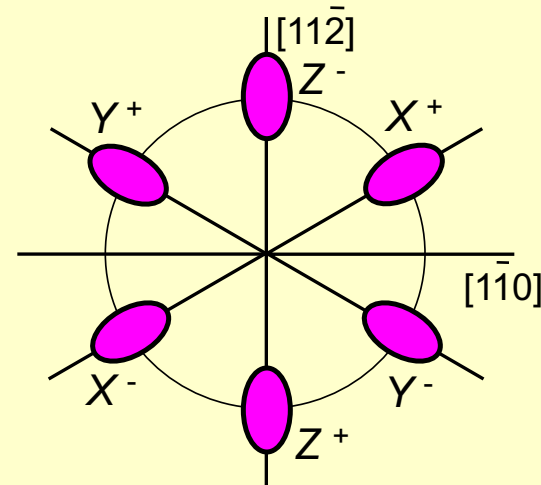
R.R. Hartmann and M.E. Portnoi, LAP LAMBERT Academic Publishing (2011)

BAND STRUCTURE OF SILICON

Brillouin zone of silicon

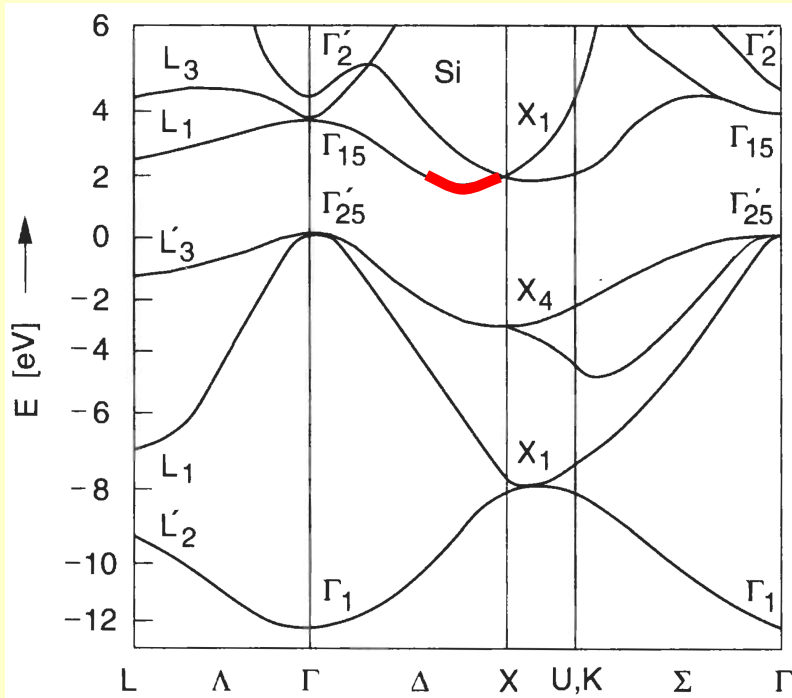


2D structure on the (111) surface



C_{3v} overall point group

C_s group of a valley



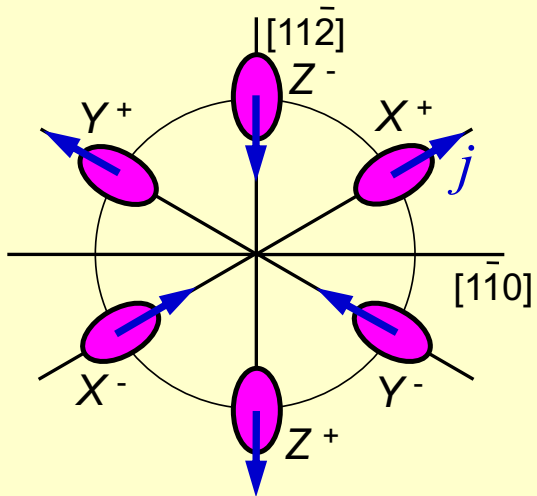
Electron dispersion in valleys

$$E_k = \frac{\hbar^2 k_{\parallel}^2}{2m_{\parallel}} + \frac{\hbar^2 k_{\perp}^2}{2m_{\perp}}$$

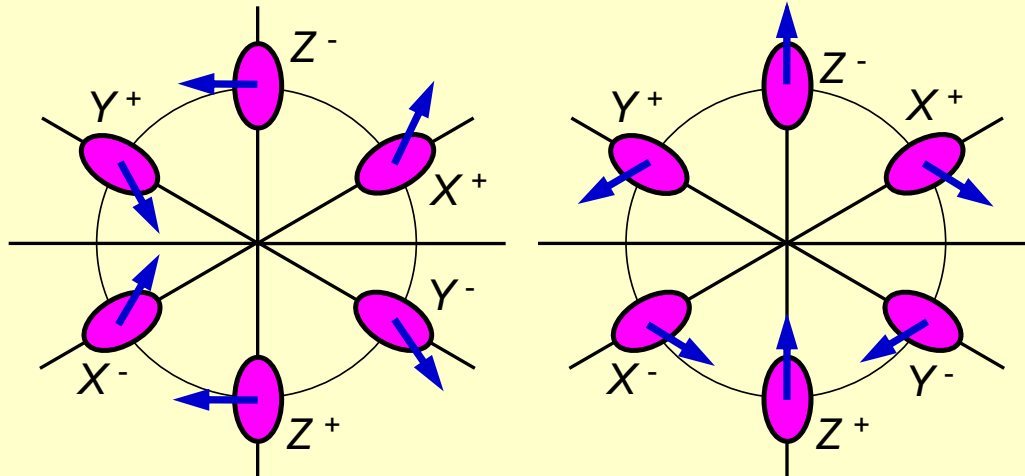
strong mass anisotropy $m_{\parallel}/m_{\perp} \approx 5$

CLASSIFICATION OF VALLEY CURRENTS

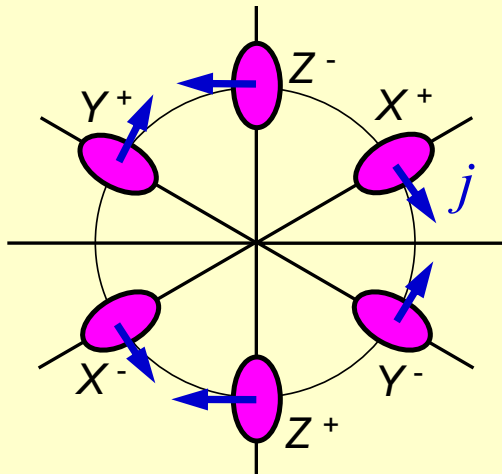
Representation A_1



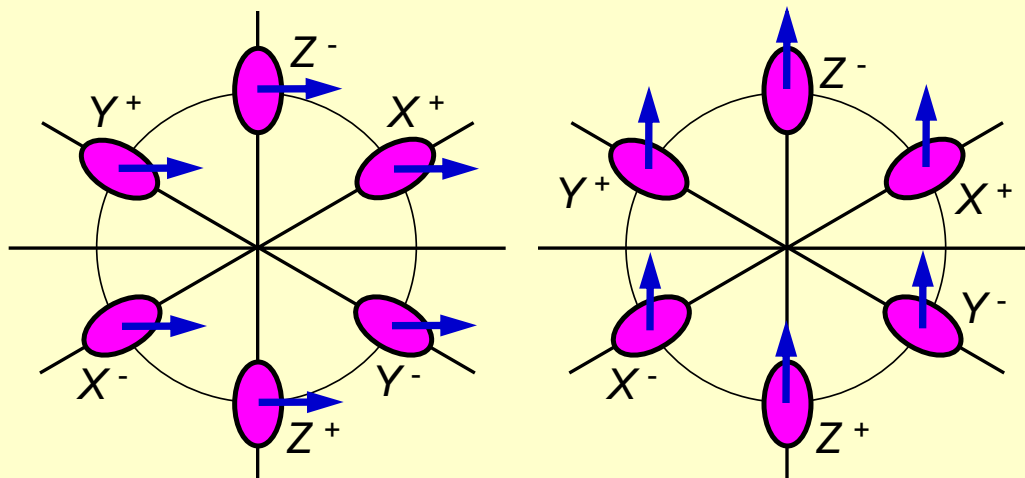
Representation E



Representation A_2

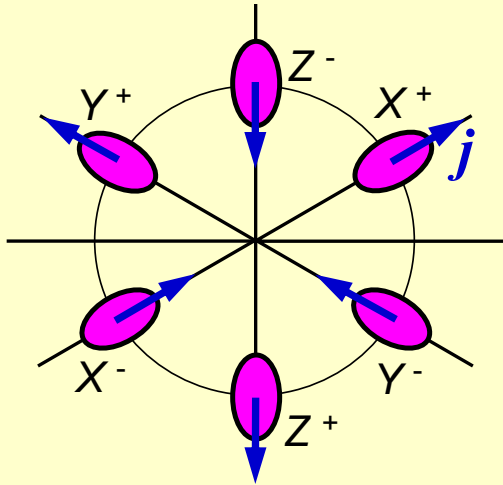


Representation E (electric current)

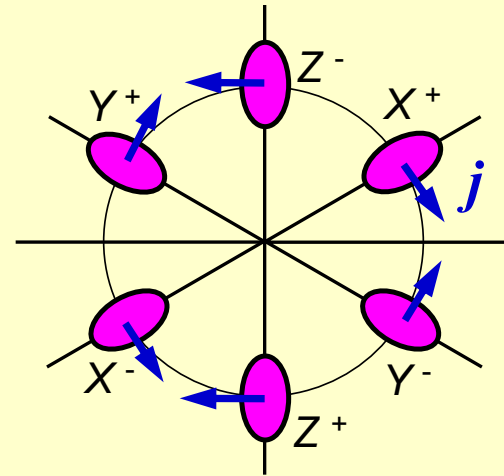


VALLEY CURRENTS IN (111) SILICON STRUCTURES

Excitation with unpolarized radiation



Circularly polarized radiation

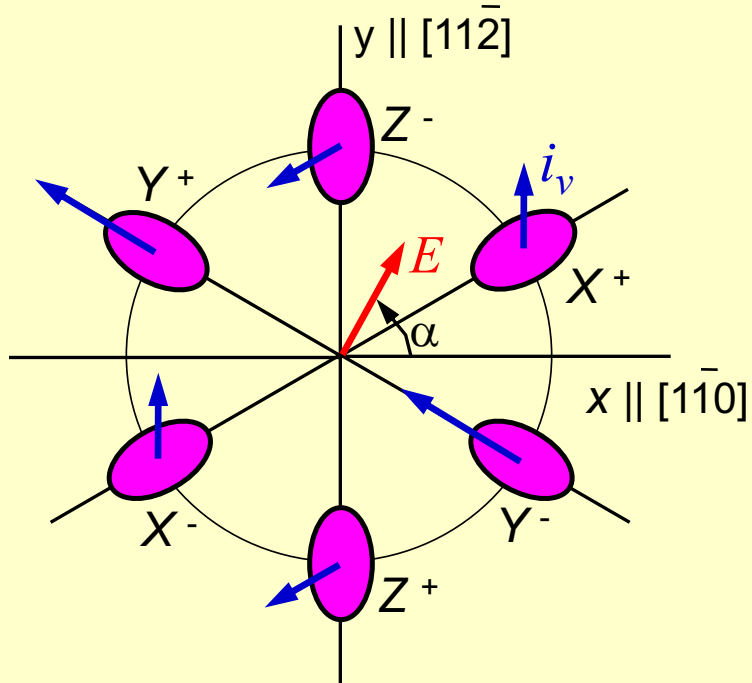


$$j_{\Sigma} = \sum_v j_v$$

net electric current

EXCITATION WITH LINEARLY POLARIZED RADIATION

Photocurrent distribution

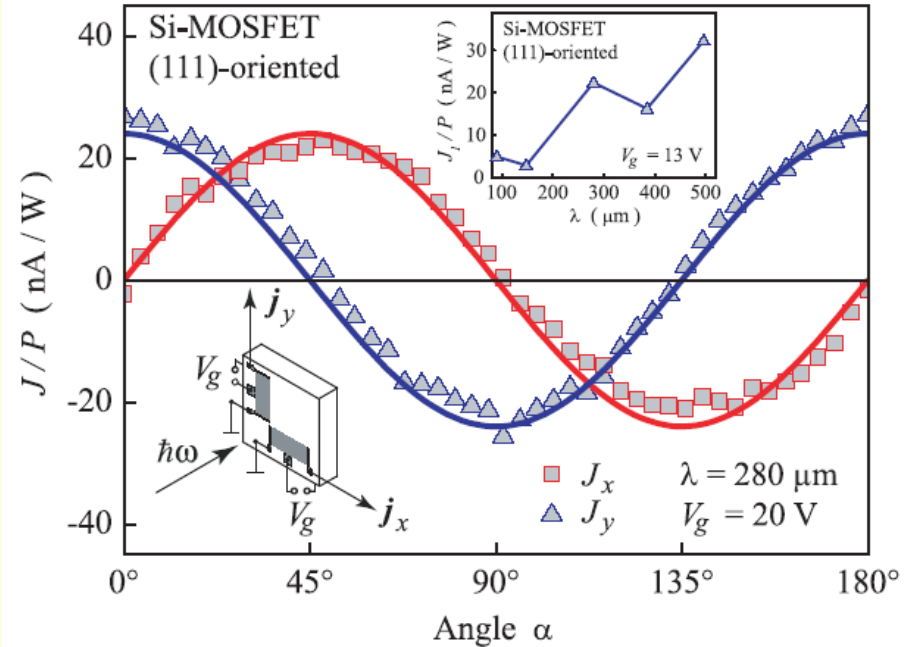


Total electric current

$$J_x / I = \sum_v j_{v,x} / I = -3(B + D)(e_x e_y^* + e_y e_x^*) \propto \sin 2\alpha$$

$$J_y / I = \sum_v j_{v,y} / I = -3(B + D)(|e_x|^2 - |e_y|^2) \propto \cos 2\alpha$$

Polarization dependence of current

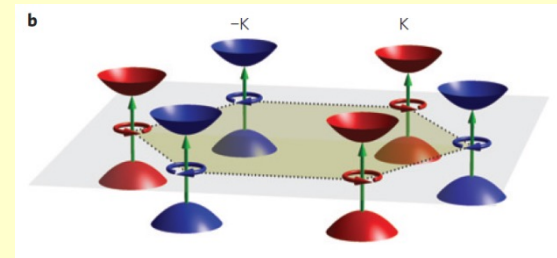
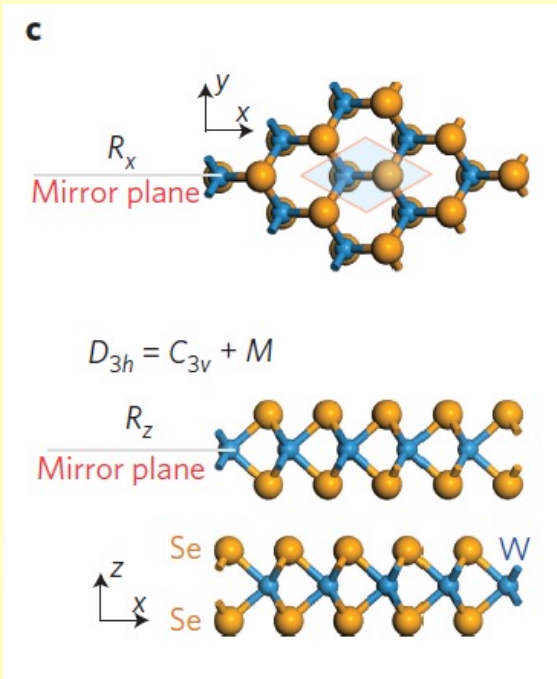


(111) Si-MOS structure, room temperature

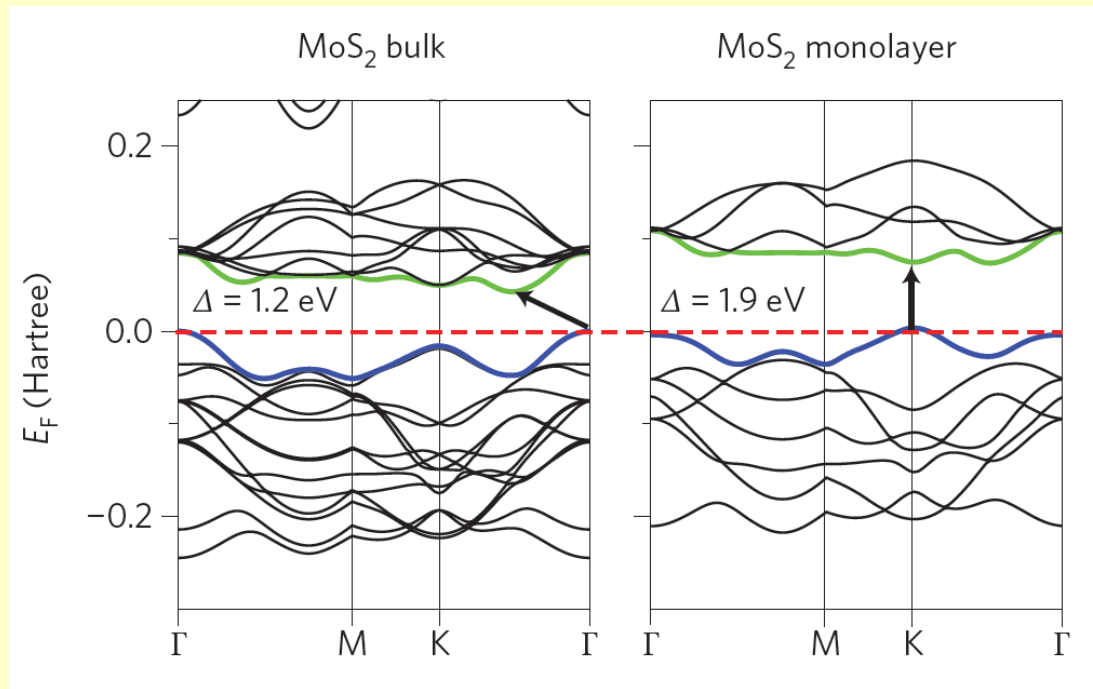
TRANSITION METAL DICHALCOGENIDES

MX_2 (M = Mo, W; X = S, Se)

Crystal structure



Band structure of bulk material and monolayers



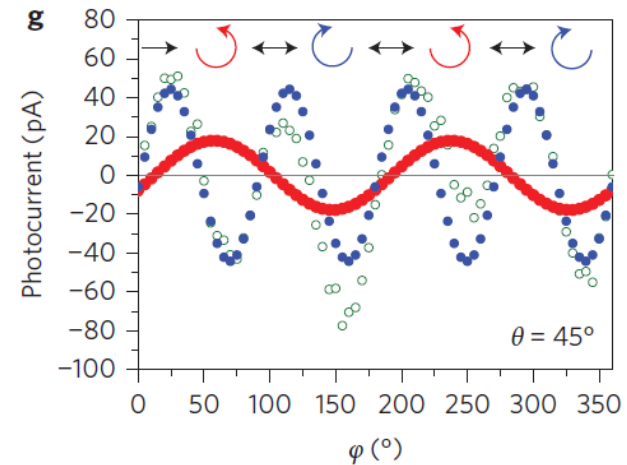
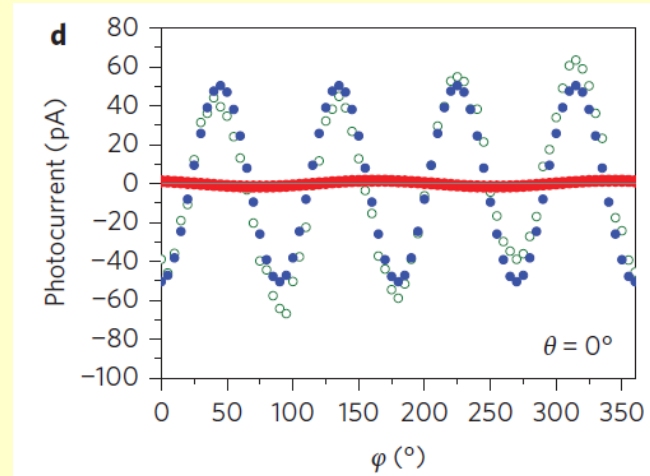
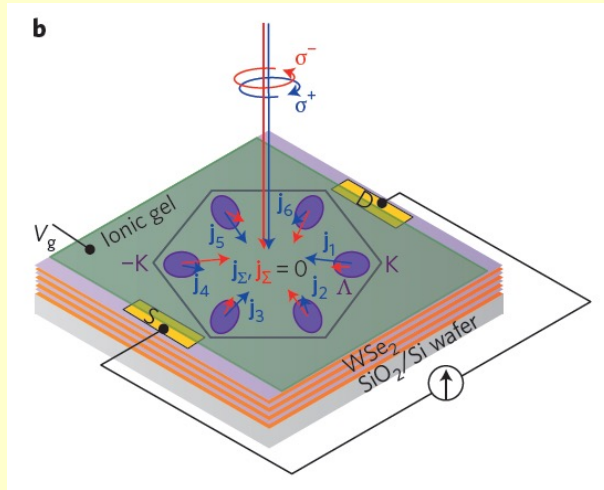
Q. H. Wang et al., Nature Nanotech. **7**, 699 (2012)

X. Xu et al., Nature Phys. **10**, 343 (2014)

Excitons: G. Wang, A. Chernikov, M.M. Glazov et al.,
Rev. Mod. Phys. **90**, 021001 (2018)

VALLEY PHOTOCURRENTS IN WSe₂ LAYERS

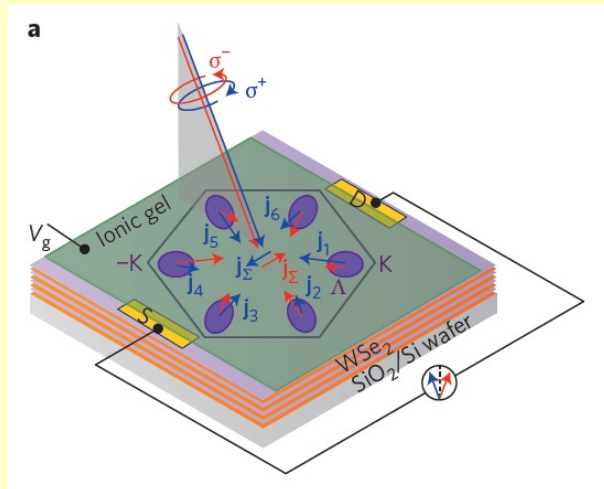
Normal incidence of circularly polarized light



Oblique incidence of circularly polarized light

C_{3v} overall point group

C_1 group of a valley



H. Yuan et al., Nature Nanotech. **9**, 851 (2014)
S.A.T., Nature Nanotech. **9**, 752 (2014)

Valley photocurrents in TMDC, Weyl semimetals, etc.

ФОТОГАЛЬВАНИЧЕСКИЕ ЭФФЕКТЫ

- Фотогальванические эффекты и эффекты хруповика в двумерных системах без центра инверсии. Инструмент изучения симметрии системы, электрон-фотонного взаимодействия, процессов релаксации
- Спиновые и долинные фототоки (в графене, TMDC слоях, Si, полуметаллах Вейля и др.). Электрический ток определяется суммой парциальных вкладов и отсутствует для чисто спиновых/долинных токов

